



X-ray photoelectron spectroscopy: how does it work and what can we learn from it?

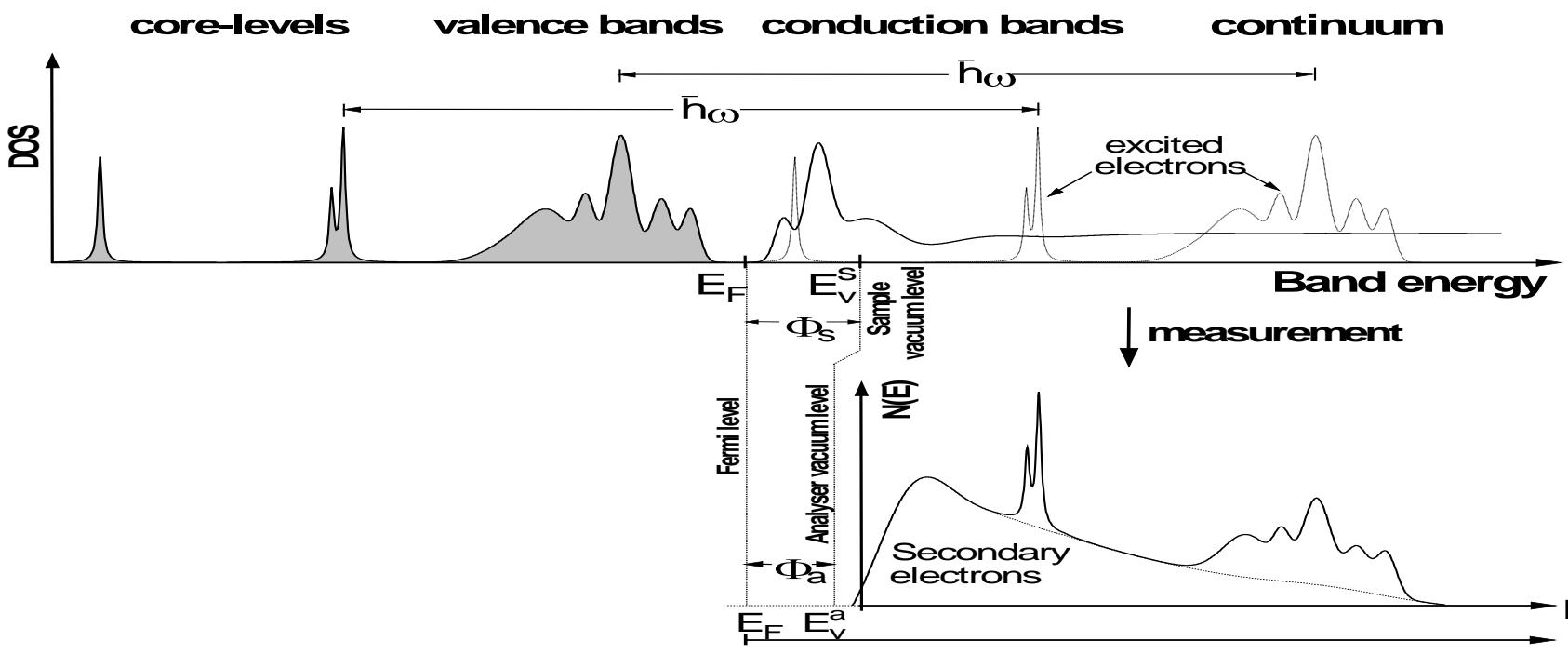
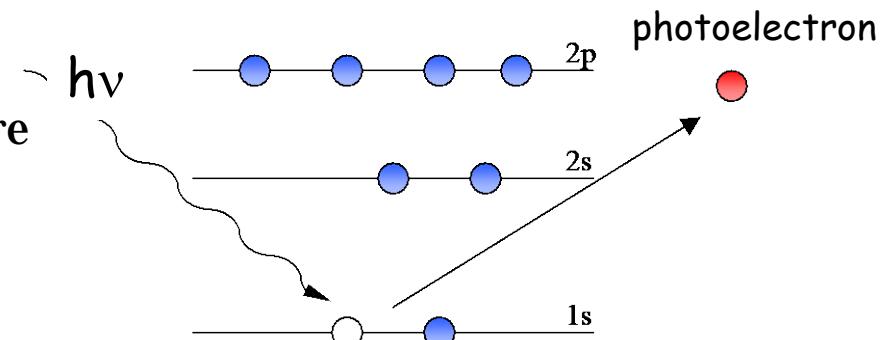
Petra Rudolf

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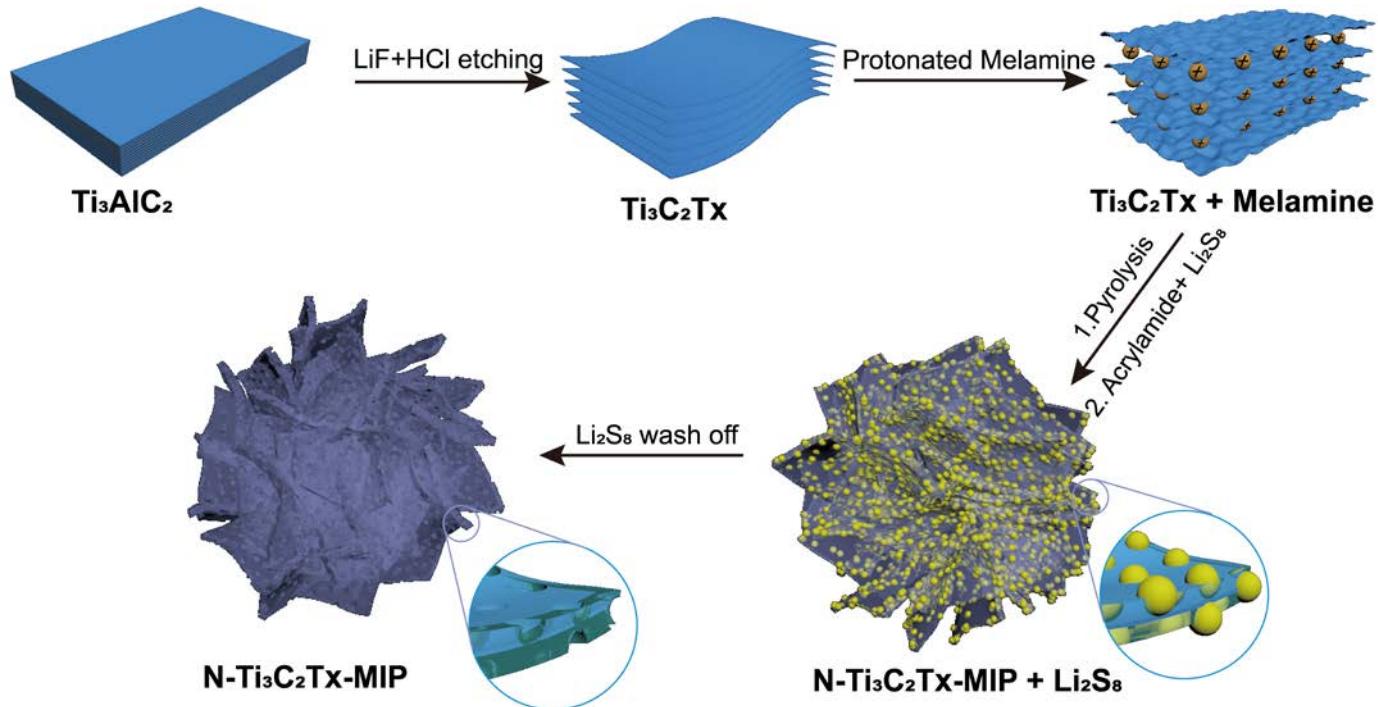
How does it work?

- monochromatic X-rays, UV light
- measure kinetic energy of emitted electrons
- deduce binding energy from electronic structure



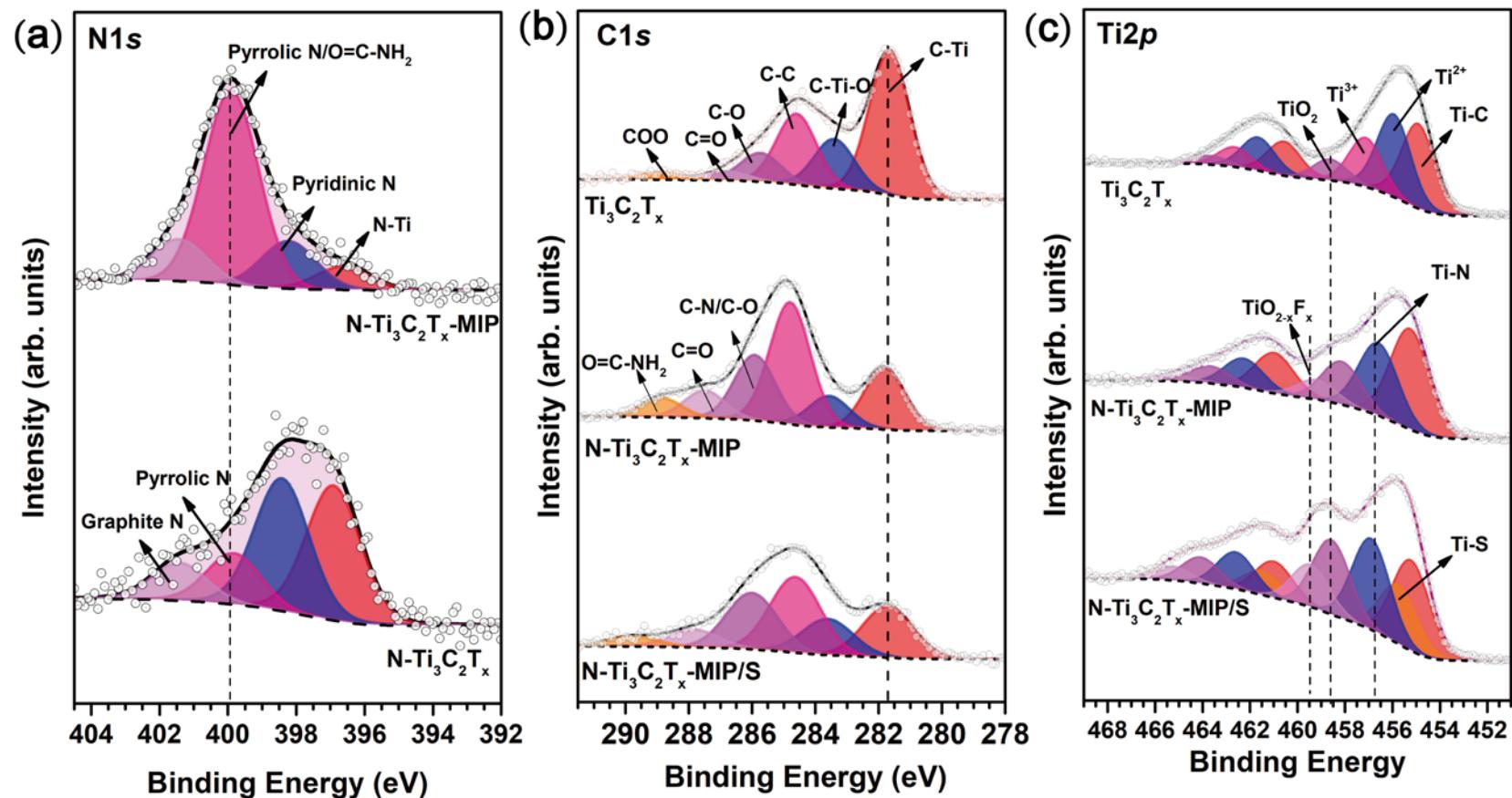


Molecularly imprinted polymer (MIP) in conjunction with 2D material, MXene, developed for cathodes of Li-S batteries



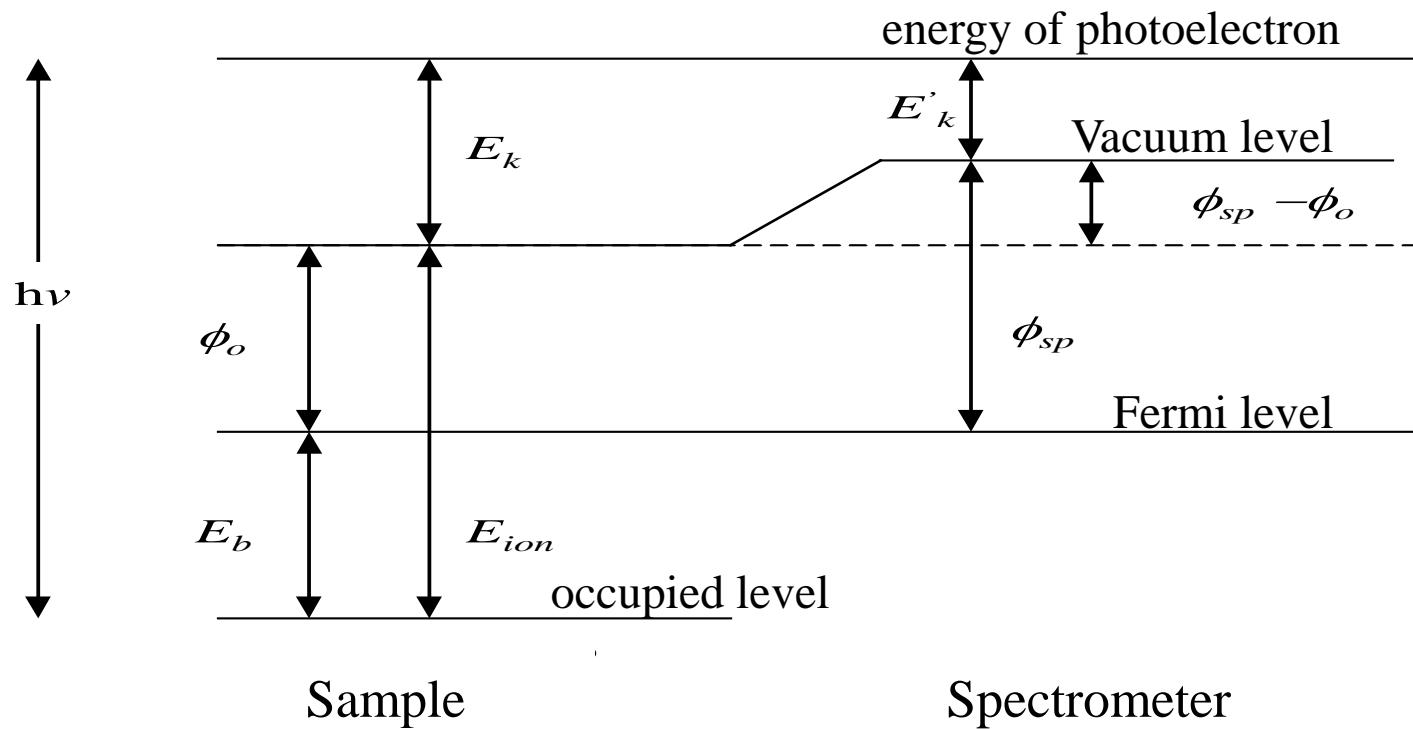


Molecularly imprinted polymer (MIP) in conjunction with 2D material, MXene, developed for cathodes of Li-S batteries





What is the binding energy in XPS ?



$$h\nu = E_b + E_k + \phi_0$$

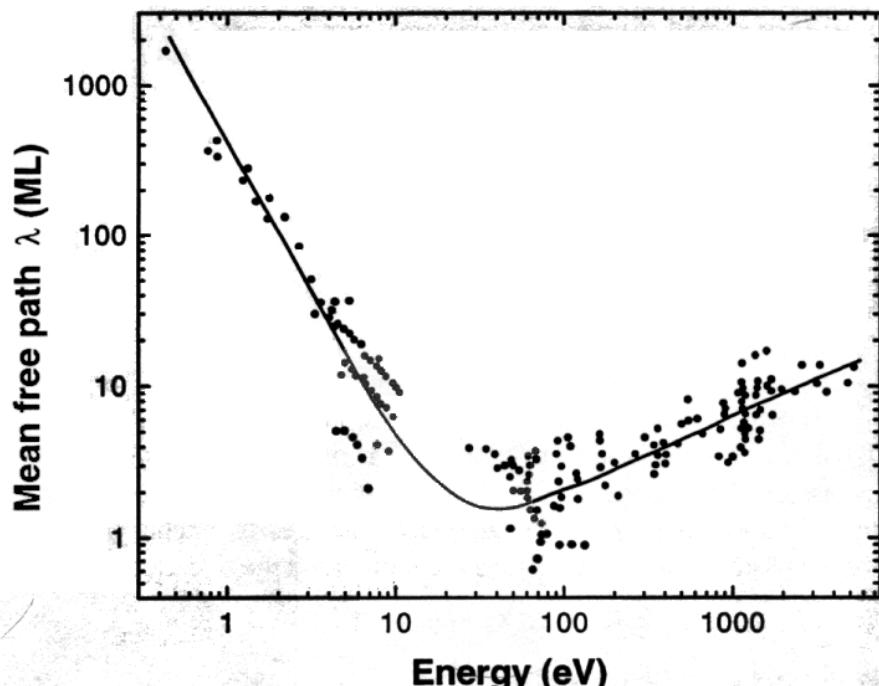
$$E_b = E_f - E_i = h\nu - E'_{k'} + \phi_{sp}$$



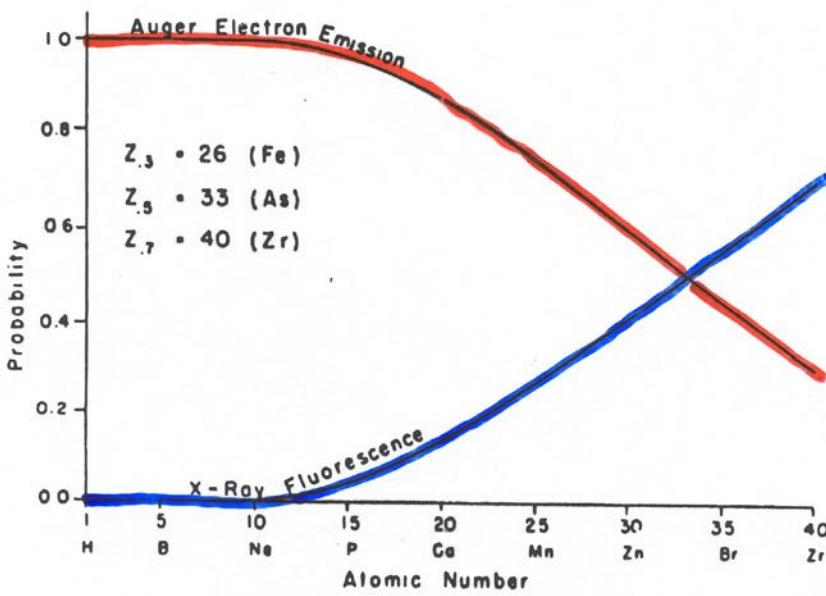
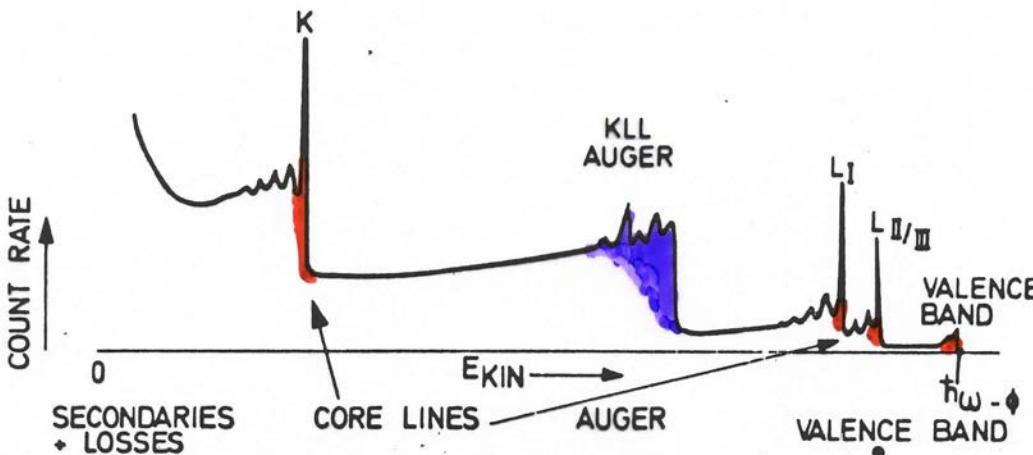
Photoemission can be seen as 3 step process

- 1) photoionisation - optical absorption machinery, selection rules
- 2) transport of photoelectron through sample - inelastic mean free path
- 3) emission of photoelectron into vacuum - refractive effects at the surface, k-parallel vs. k-normal

Universal curve of electron mean free path (Zangwill '88)



$E_k < 1500 \text{ eV}$: XPS
gives information on
surface layer (typically
 $< 10 \text{ nm}$)



The photoionisation of core level
→ Auger decay or fluorescent
decay (X-ray emission)

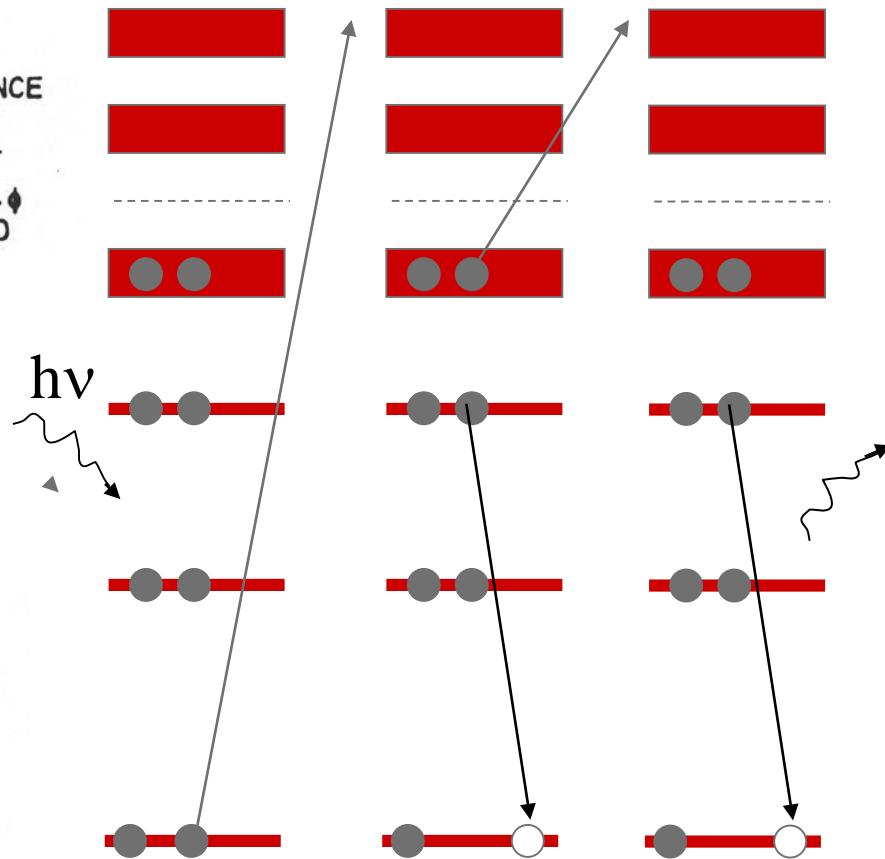
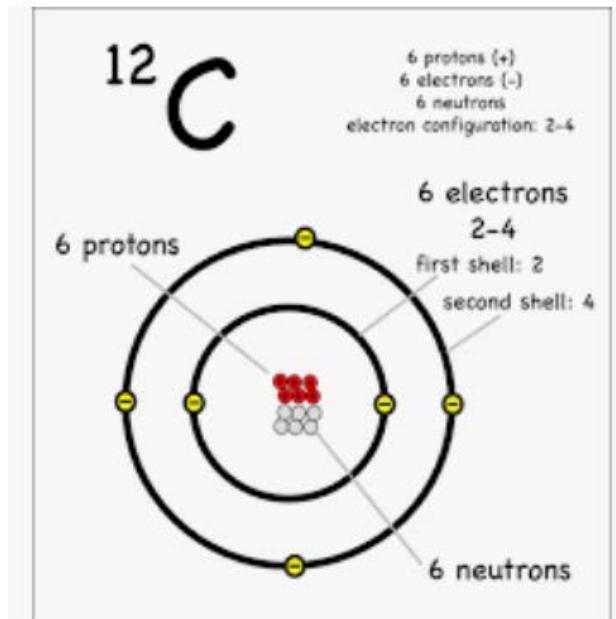


Figure 3.5 Relative probabilities of relaxation by emission of an Auger electron and by emission of an X-ray photon of characteristic energy, following creation of a core hole in the K shell



Let's start simple: Carbon



C: $1s^2 2s^2 2p^2$



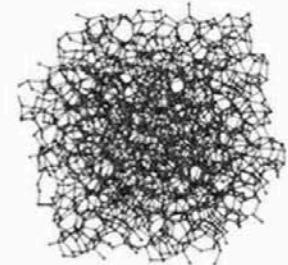
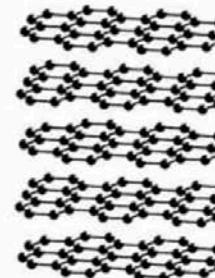
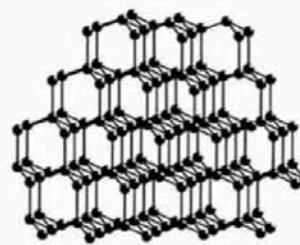
DIAMOND



GRAPHITE

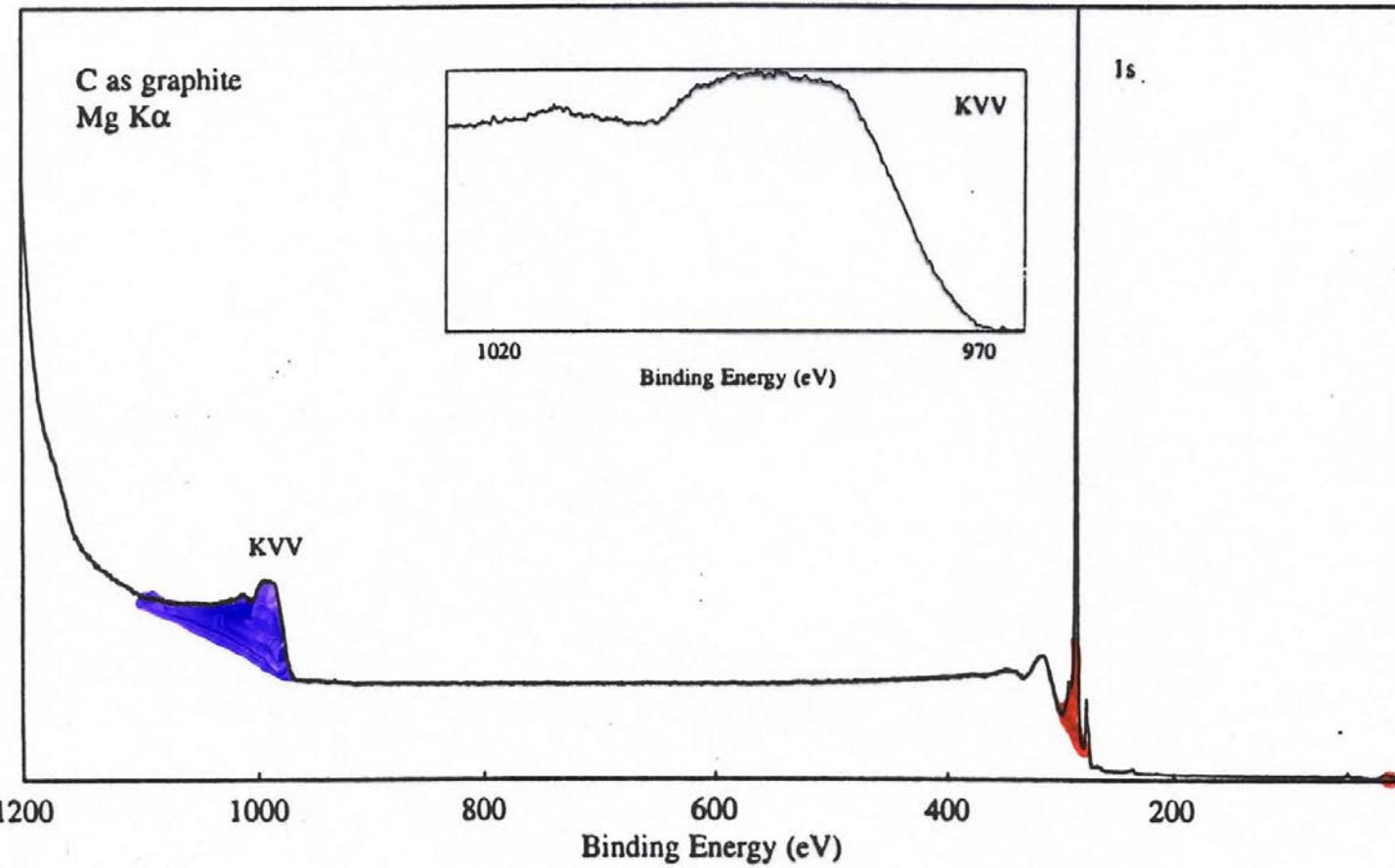


AMORPHOUS CARBON



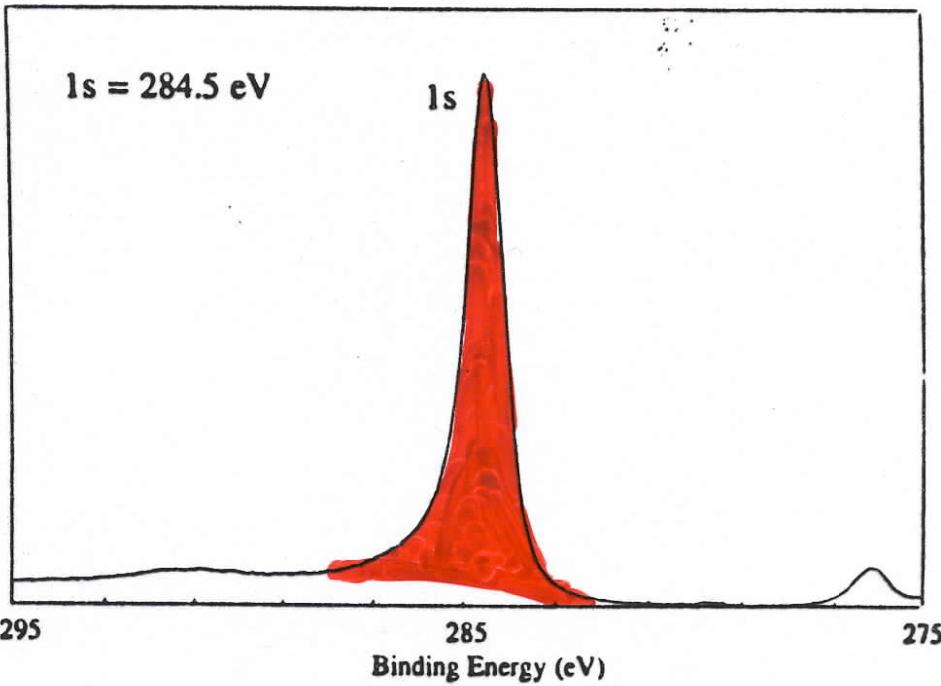


Wide XPS spectrum of graphite (C)





Core level XPS spectrum of graphite (C)



The singlet **C 1s** line is characterized by:

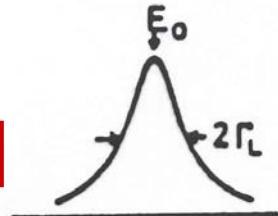
- 1) A specific binding energy which reflects the specific atomic species (C) in a specific chemical environment**

- 2) A finite width reflecting the instrumental resolution, lifetime broadening and other many-body effects**

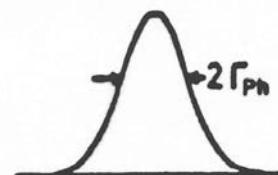


What determines the line shape ?

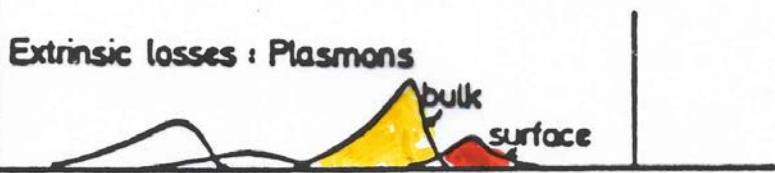
Lorentzian Lifetime broadening



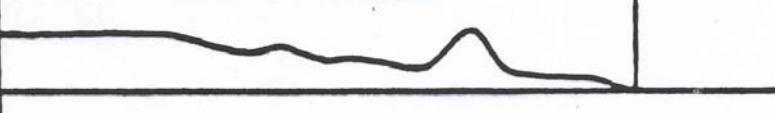
Gaussian Phonon broadening



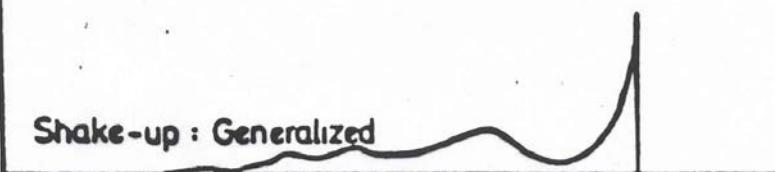
Extrinsic losses : Plasmons



Extrinsic losses : Generalized



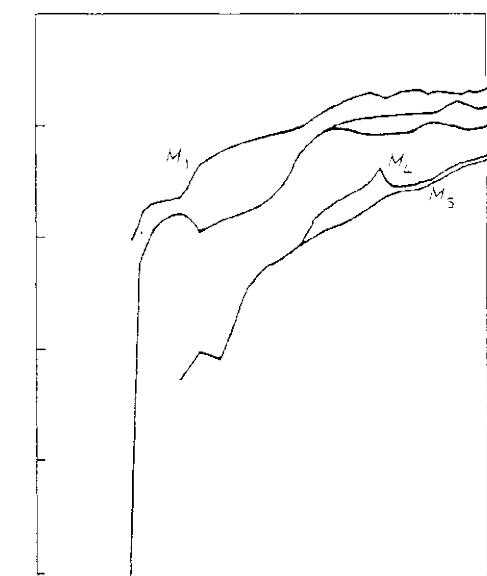
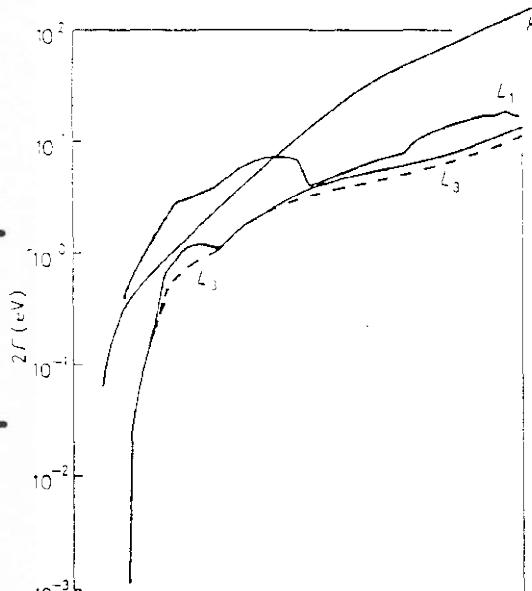
Shake-up : Generalized



— K. E. —

photoionisation process takes 10^{-17} sec – core hole of light element decays in 10^{-15} sec – indetermination in energy

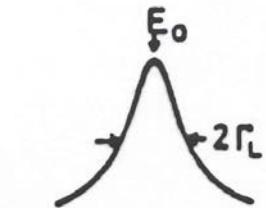
$$\frac{1}{2} \text{FWHM} = \Gamma_L = h/\tau = 6.58 \cdot 10^{-16}/\tau \text{ eV},$$



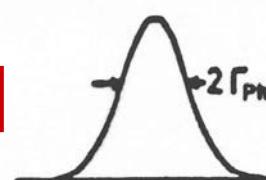


What determines the line shape ?

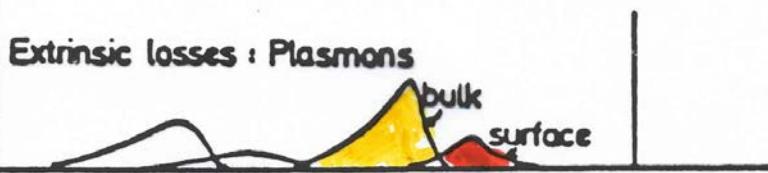
Lorentzian Lifetime broadening



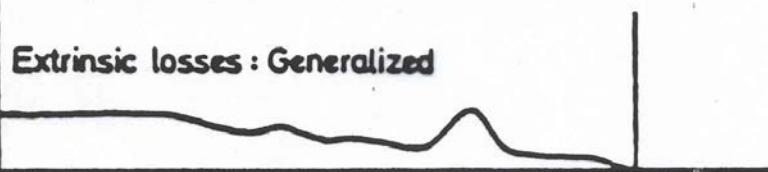
Gaussian Phonon broadening



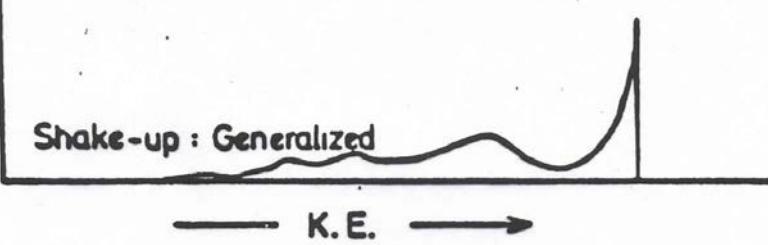
Extrinsic losses : Plasmons



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Shake-up : Generalized

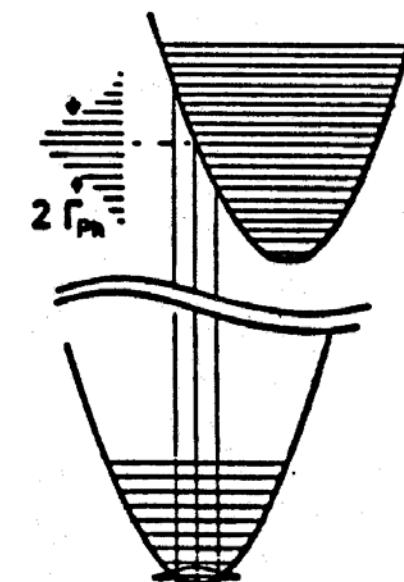


— K. E. —

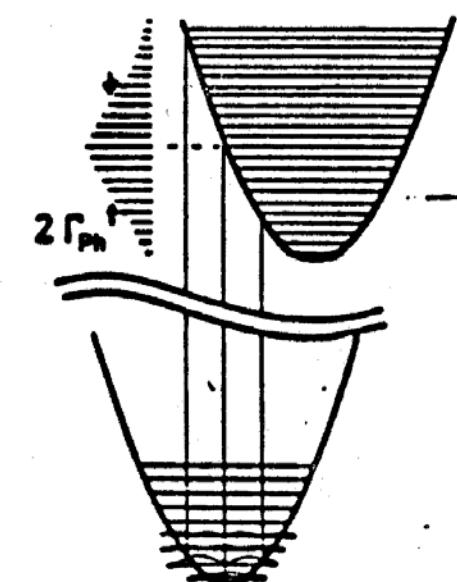
VIBRATIONAL

BROADENING

(a) $T=0$ K



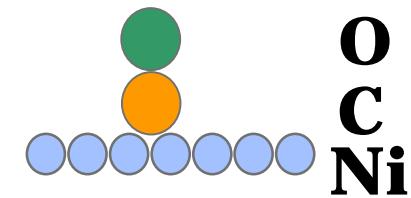
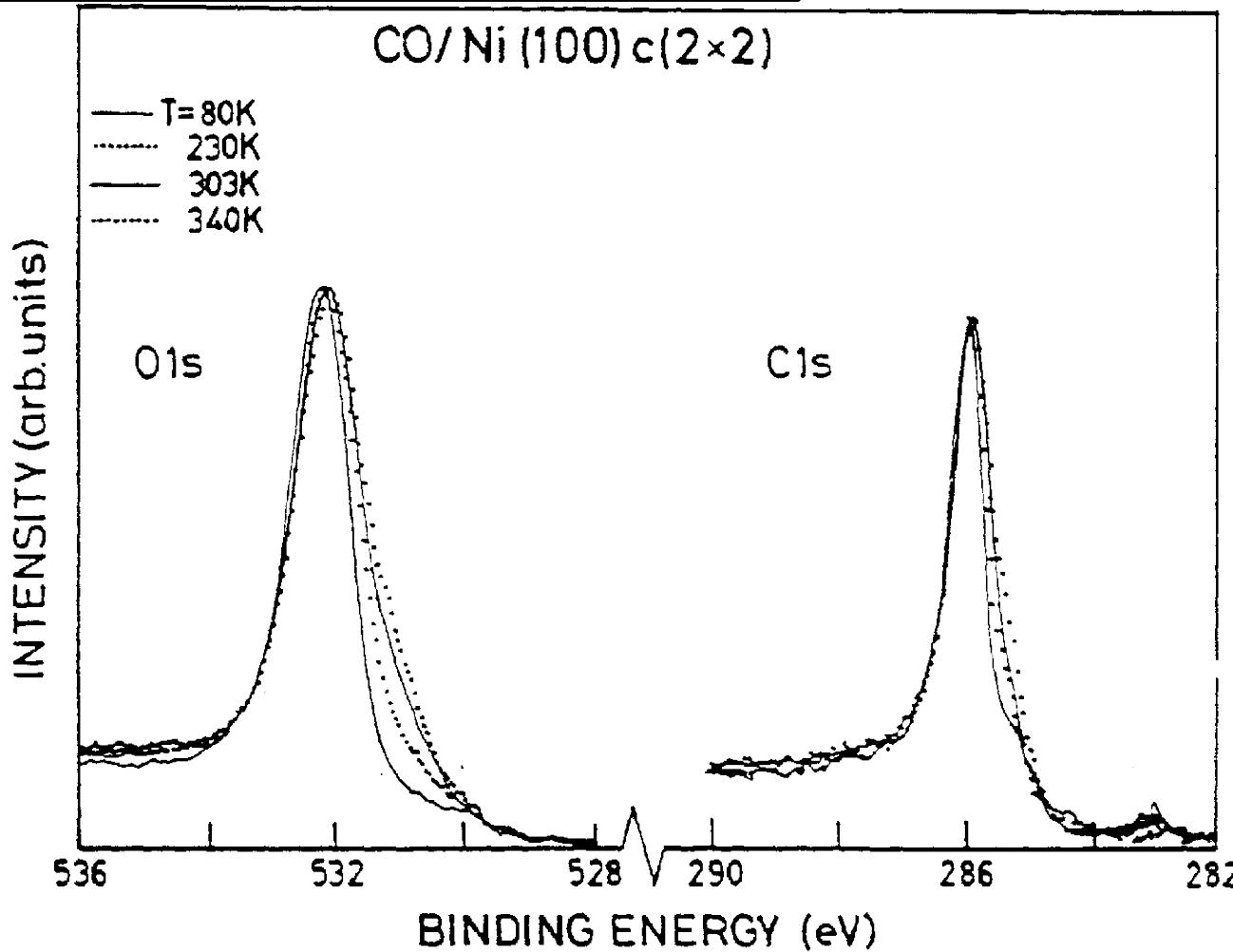
(b) $T>0$ K



The origin of phonon broadening in XPS and Auger lines



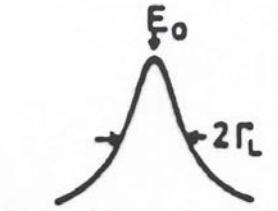
Vibrational Broadening



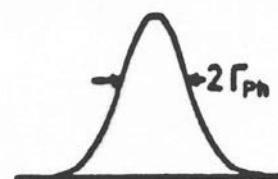


What determines the line shape ?

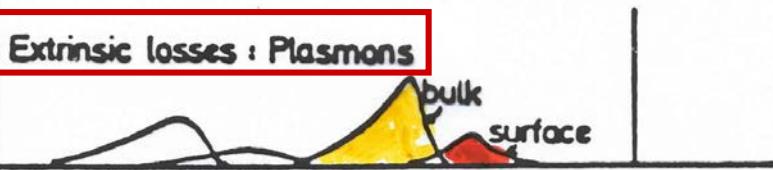
Lorentzian Lifetime broadening



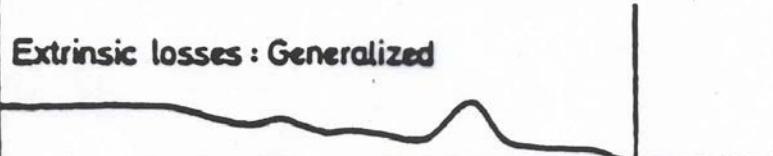
Gaussian Phonon broadening



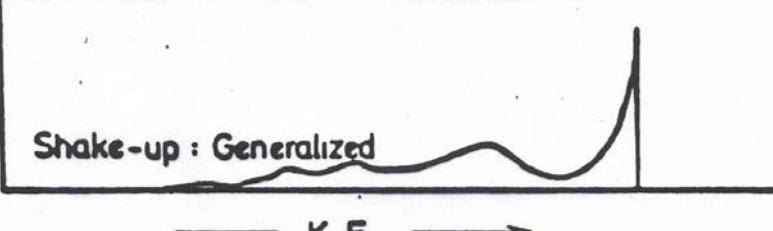
Extrinsic losses : Plasmons



Extrinsic losses : Generalized

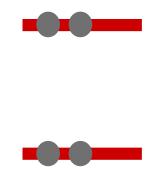
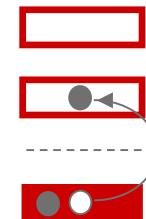
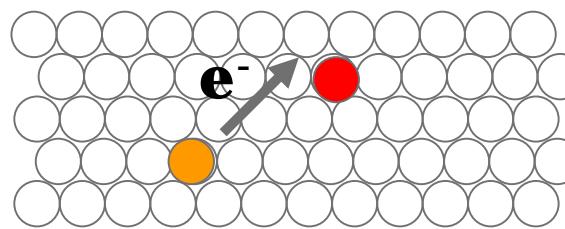


Shake-up : Generalized



— K. E. —

Extrinsic losses



- single electron transitions

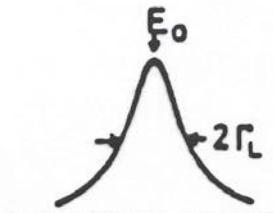
- collective excitations = plasmons

photoelectron loses energy
spectral features appear at lower
kinetic energy

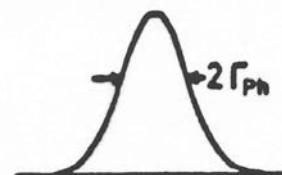


What determines the line shape ?

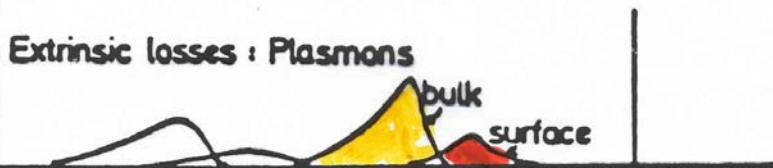
Lorentzian Lifetime broadening



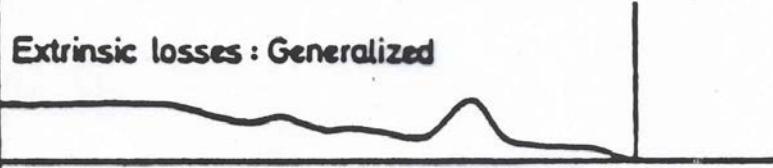
Gaussian Phonon broadening



Extrinsic losses : Plasmons



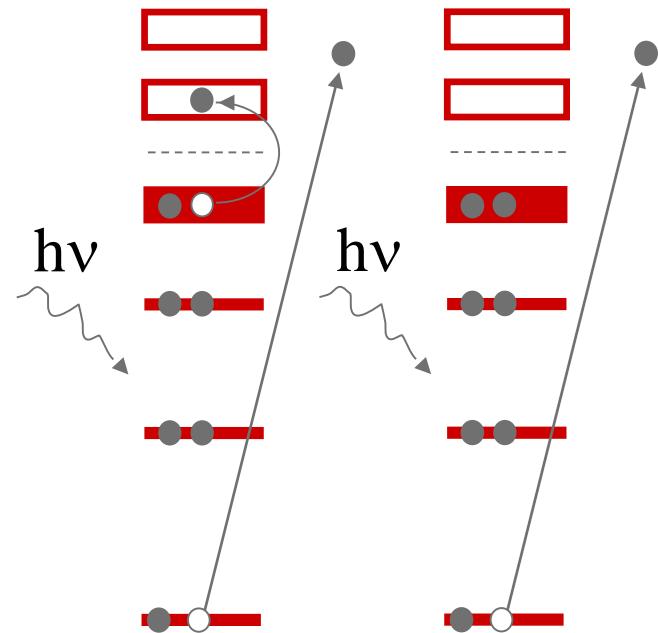
Extrinsic losses : Generalized



Shake-up : Generalized

— K. E. —

Shake-up: photoemission is not a single particle process - different final states possible





Line-asymmetry in Core Level XPS

The line-asymmetry scales with the density of states at E_F

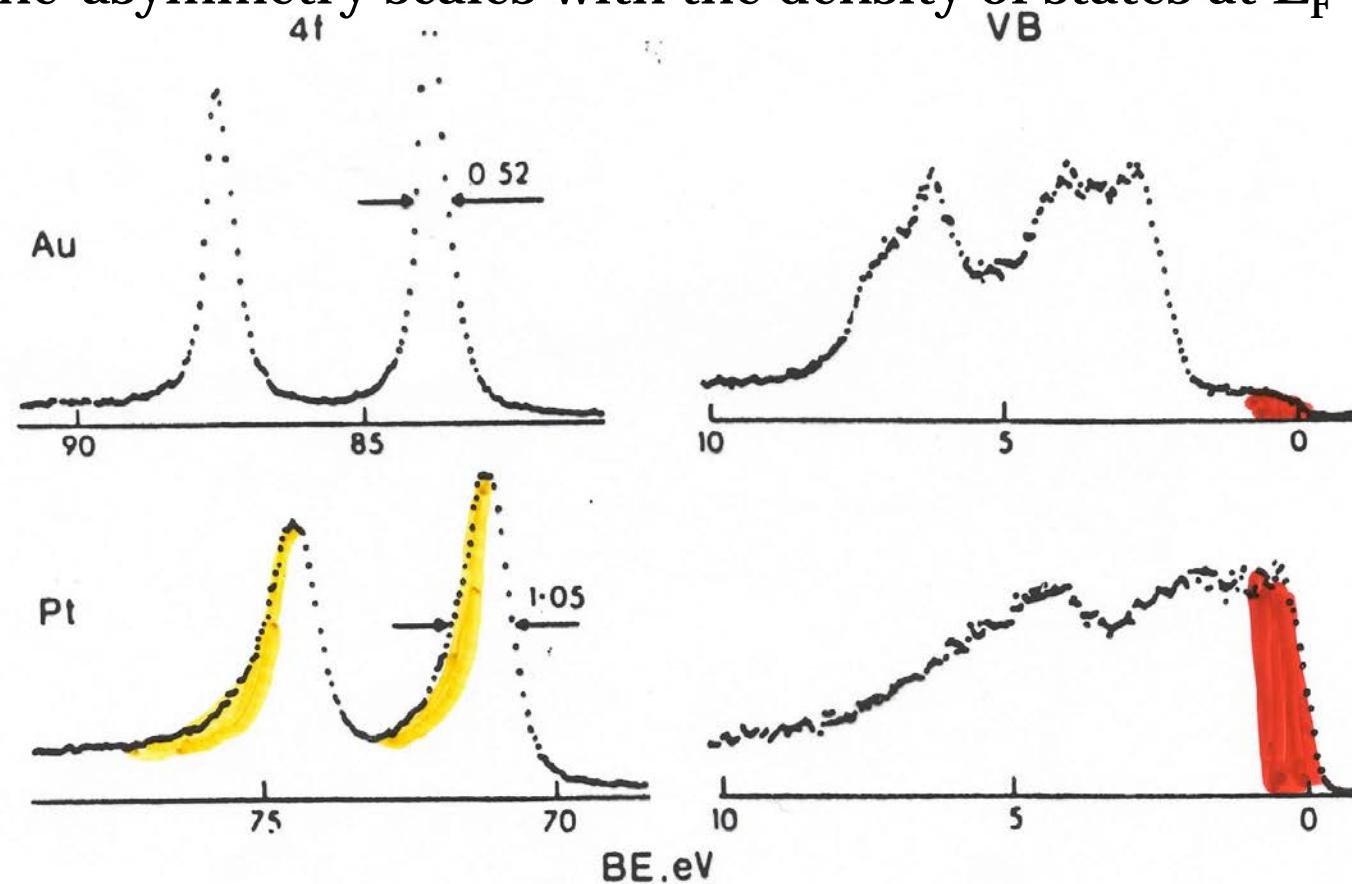
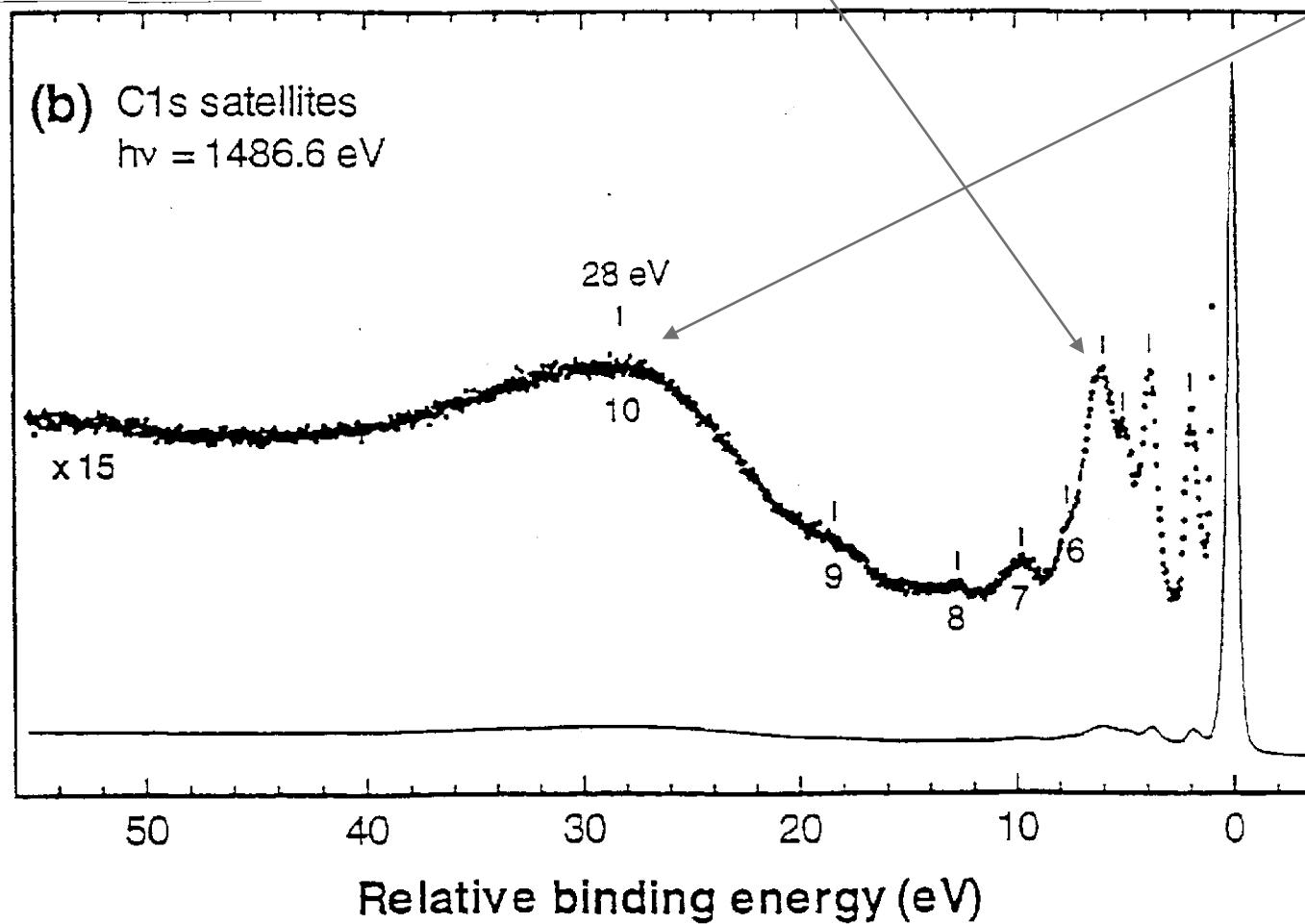


Figure 3.33. Core (4f) and valence (VB) photoelectron spectra of gold and platinum recorded using monochromatic Al K α radiation. Note the relationship between the degree of core level asymmetry and the density of states at the Fermi level (BE = 0 eV). (After Barrie, Swift and Briggs⁴⁹)



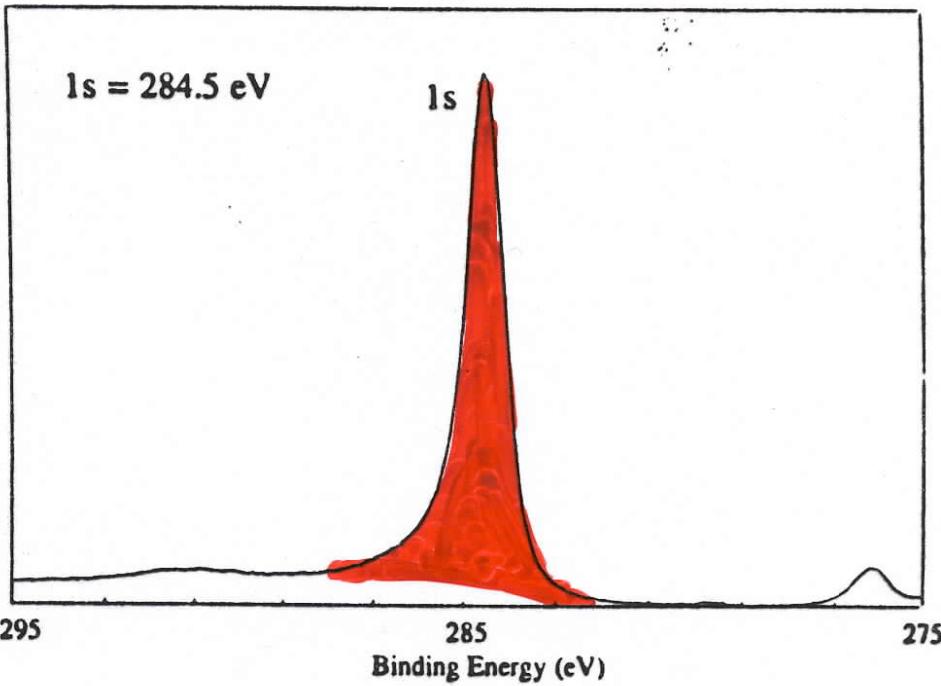
Example: **C₆₀** : 3 valence electrons of carbon form s orbitals – cage structure,
1 valence electron in π orbitals.

single electron excitations; all $\pi \rightarrow \pi^*$: π plasmon; all $\pi + \sigma \rightarrow \pi^* + \sigma^*$: $\sigma + \pi$ plasmon





Core level XPS spectrum of graphite (C)



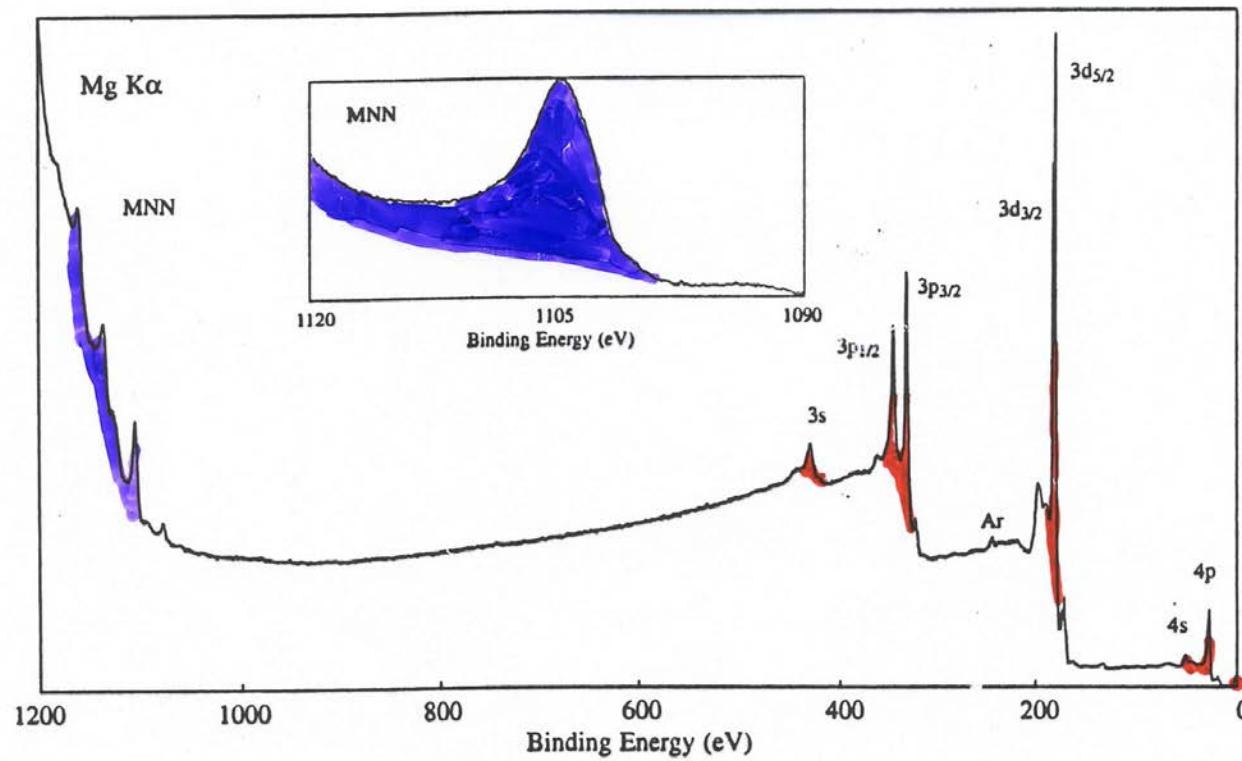
The singlet **C 1s** line is characterized by:

- 1) A specific binding energy which reflects the specific atomic species (C) in a specific chemical environment**

- 2) A finite width reflecting the instrumental resolution, lifetime broadening and other many-body effects**

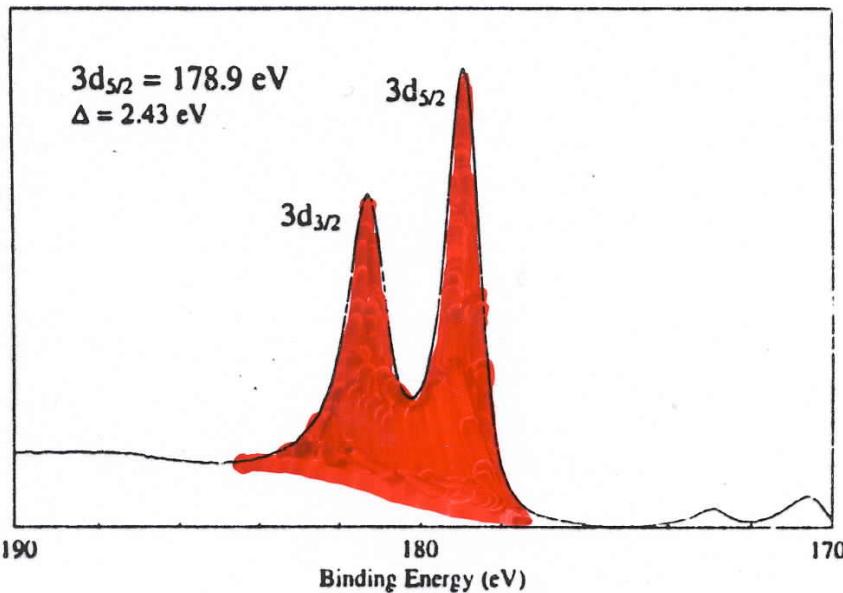


Wide XPS spectrum of zirconium (Zr)





Core level XPS spectrum of zirconium (Zr)



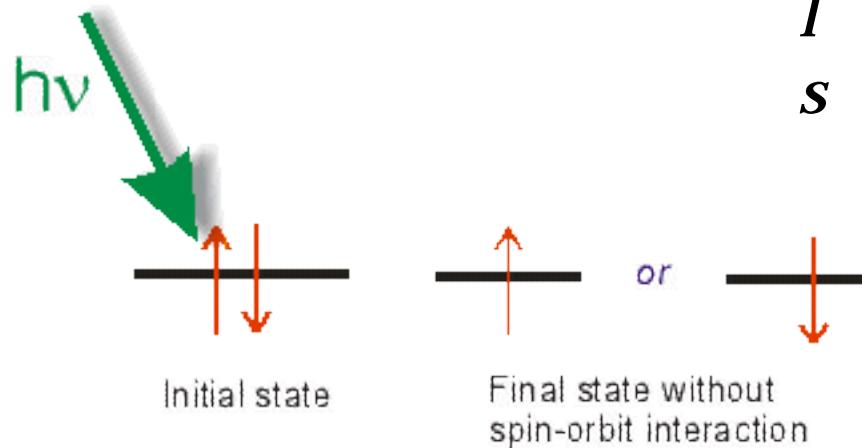
The Zr 3d line is characterized by:

- 1) A specific binding energy which reflects the specific atomic species (Zr) in a specific chemical environment
- 2) The occurrence of a doublet reflecting the core level spin-orbit splitting
- 3) A finite width reflecting the instrumental resolution, lifetime broadening and other many-body effects



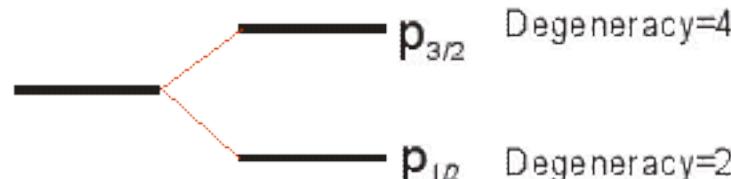
Spin-Orbit Splitting

(i)



(ii)

Spin orbit interaction lifts degeneracy



Quantum Numbers

- j Total Angular Momentum
- l Orbital Angular Momentum
- s Spin Angular Momentum

$$j = l + s$$

p-symmetry state

$$l = 1$$

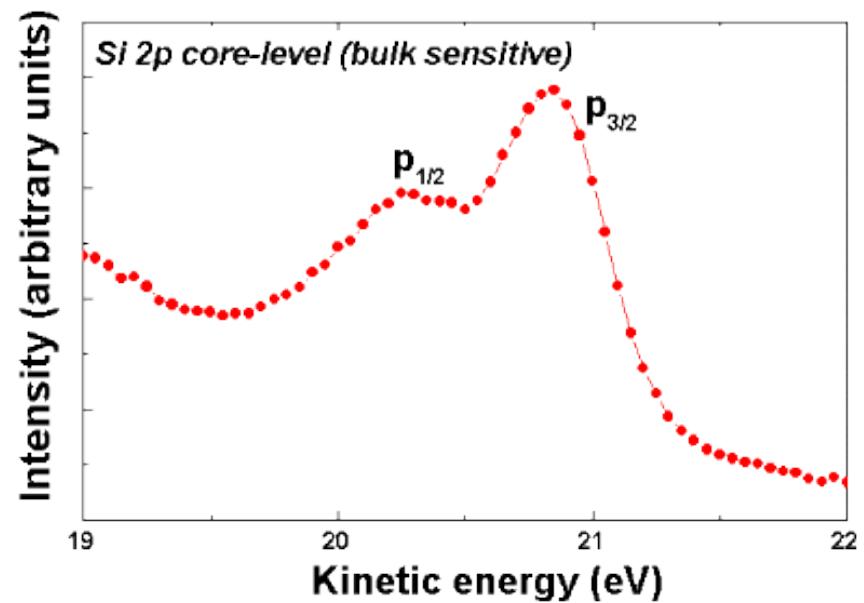
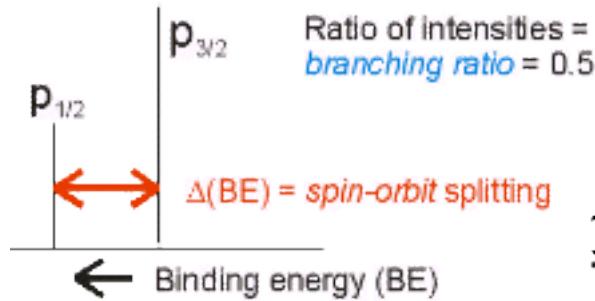
$$s = \pm 1/2$$

Degeneracy = $|2j+1|$



Spin-Orbit Splitting

(iii) Degeneracies determine relative intensities of peaks comprising doublet



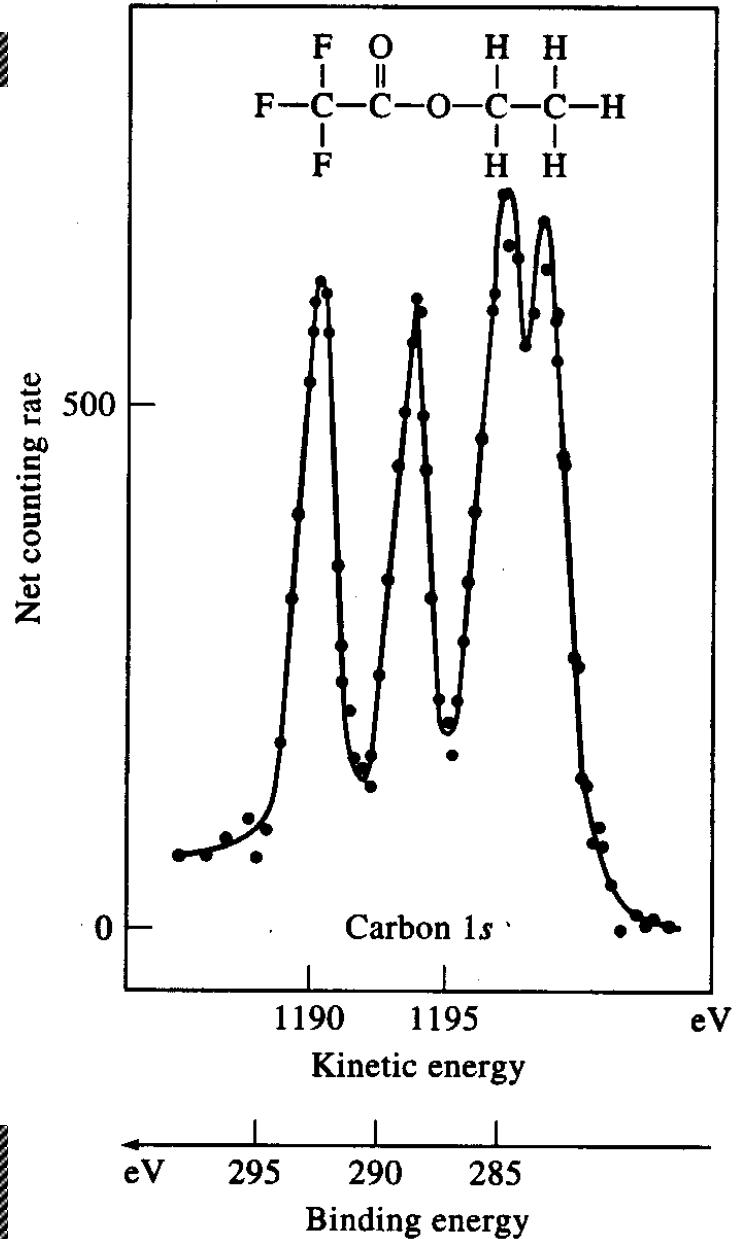


XPS : Chemical shift

Carbon 1s binding energies in ethyl trifluoroacetate

Can be used to quantify different chemical bonds for same element

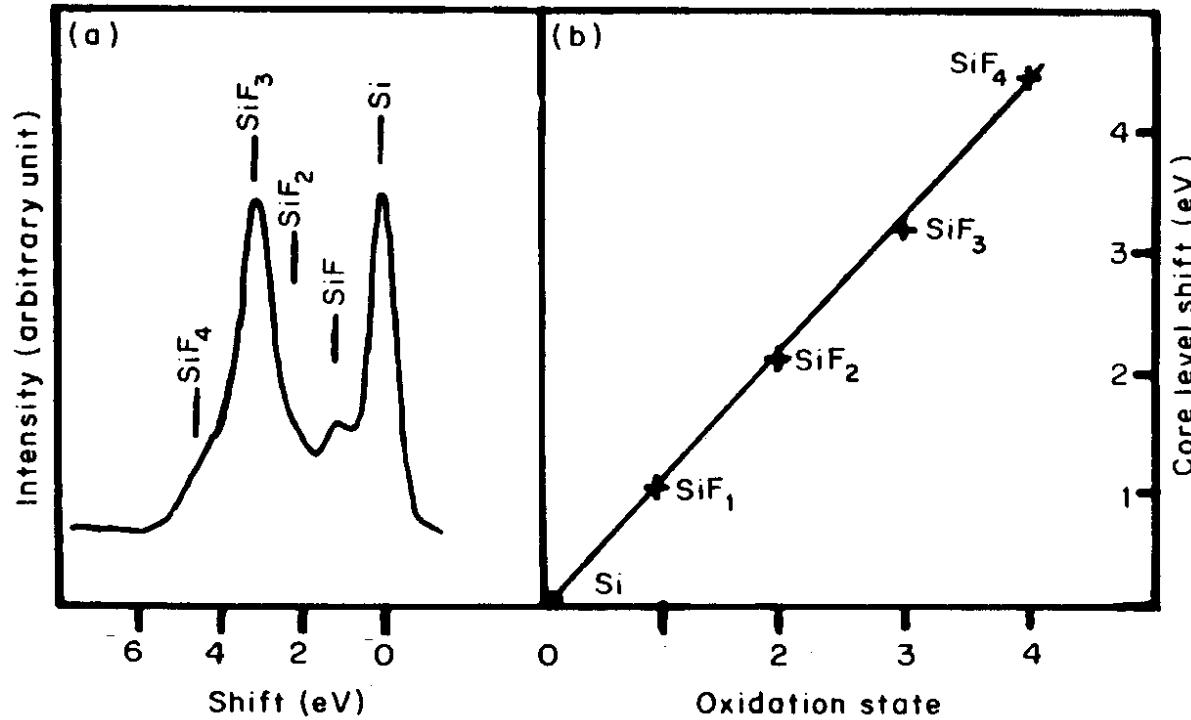
XPS also called **ESCA** -
electron spectroscopy
for chemical analysis





XPS : Chemical shift

Si 2p spectra for a fluorine-etched silicon wafer

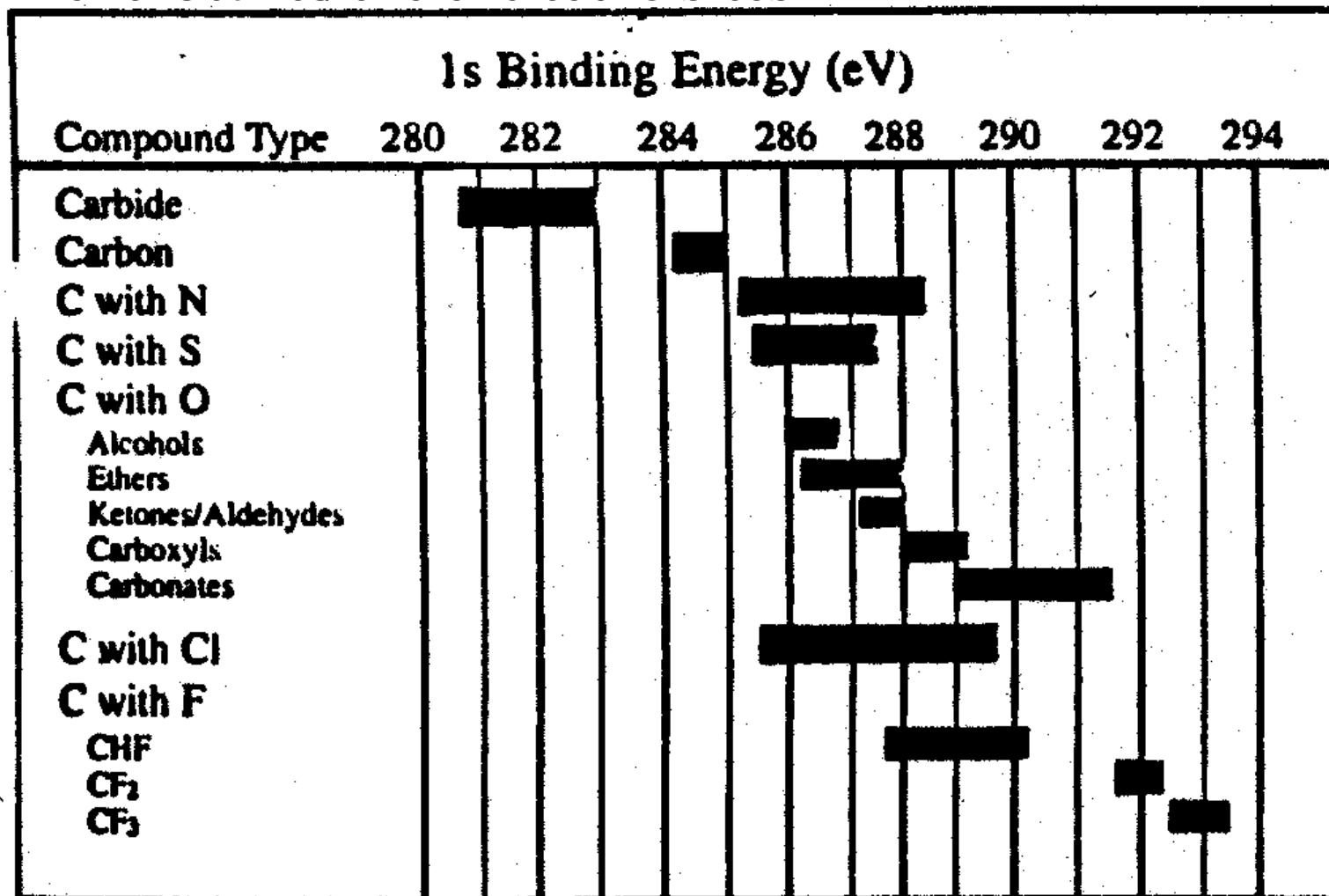


binding energies increase as the oxidation state increases - can be used to determine oxidation state



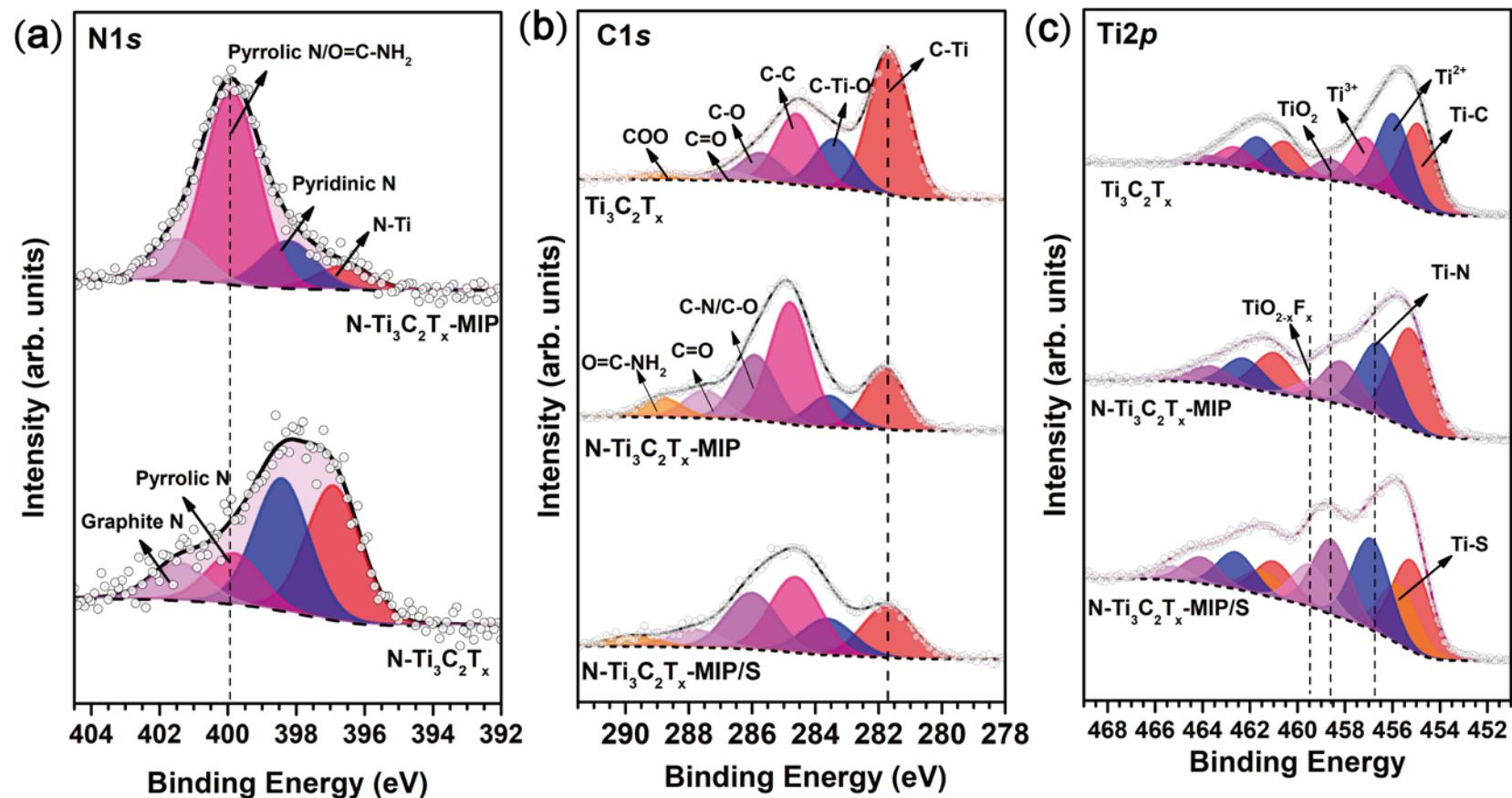
Chemical Shift (ΔE_b)

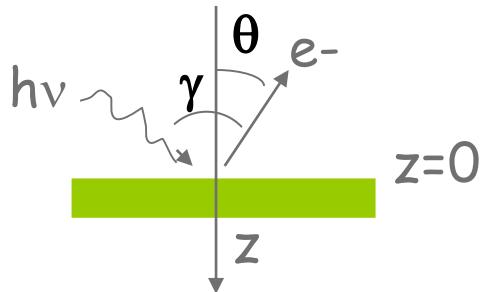
How the C 1s binding energy reflects differing chemical environment local to the excited C sites





Molecularly imprinted polymer (MIP) in conjunction with 2D material, MXene, developed for cathodes of Li-S batteries





Once the photon flux Φ is given, the photoelectron intensity I_i of the (nl) orbital of the i -th atomic species is approximately given by

$$I_i(nl) = C_i \lambda(E_{kin}) \phi(\hbar\omega) \sigma_{nl}(\hbar\omega) T(E_{kin})$$

Where Φ is the photon flux

C_i Atomic Concentration of the i -th species

λ Escape Depth

σ_{nl} Orbital Cross Section

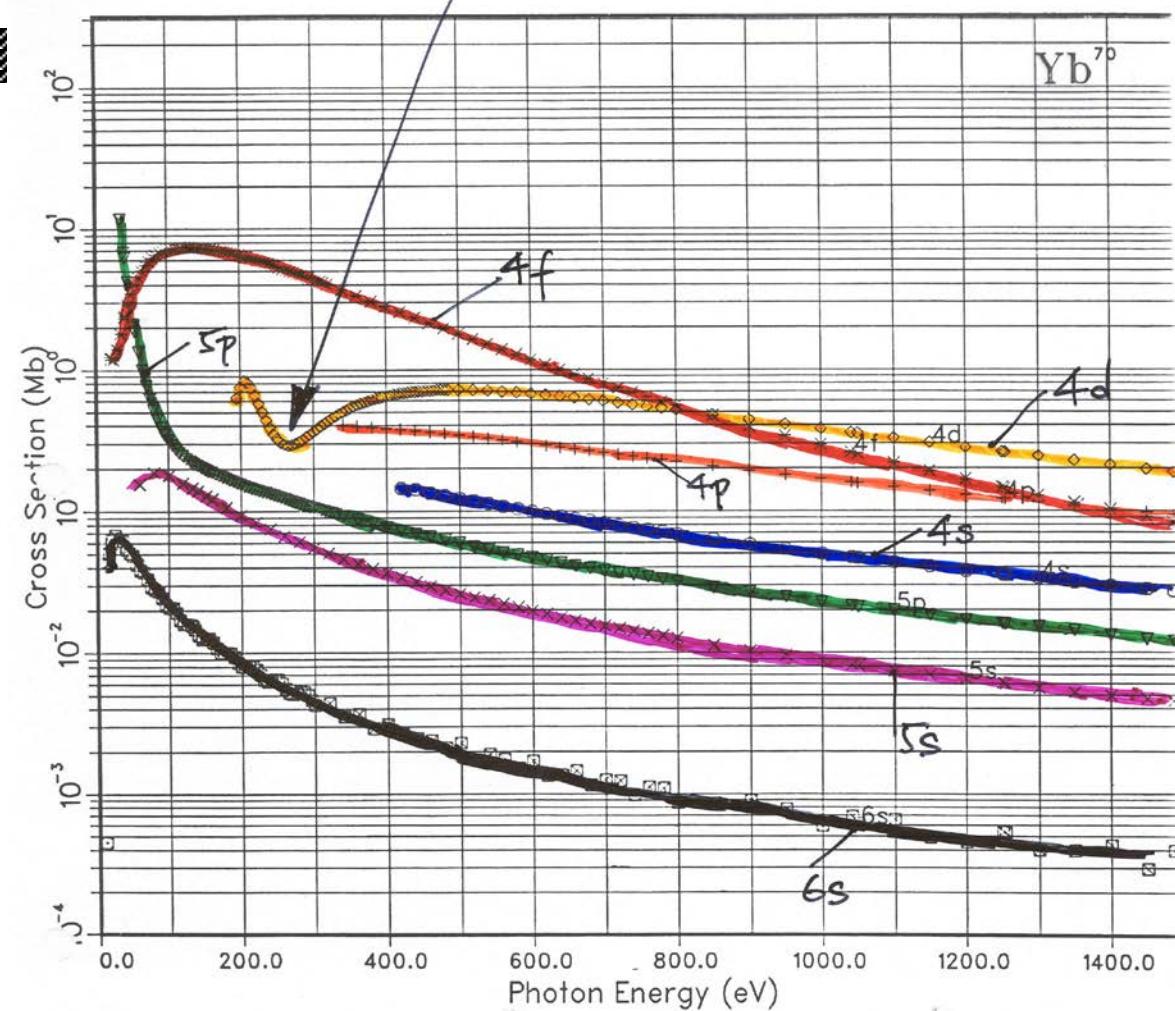
T Instrumental Efficiency

sensitivity factor $S_i = \sigma_i(h\nu) T (E_{kin})$



/ university of

COOPER MINIMUM



Calculated
photoionization cross
sections for free atoms
vs. photon energy
(Yeh and Lindau)



Appendix E. Atomic Sensitivity Factors for X-ray Sources at 90°

This table is based upon empirical peak area values* corrected for the system's transmission function. The values are only valid for and should only be applied when the electron energy analyzer used has the transmission characteristics of the spherical capacitor type analyzer equipped with an Omni Focus III lens supplied by Perkin-Elmer. The data are calculated for x-rays at 90° relative to the analyzer.

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Element	Line	ASF									
Ag	3d	5.198	Eu	4d	2.210	Na	1s	1.685	Si	2p	0.283
Al	2p	0.193	F	1s	1.000	Nb	3d	2.517	Sm	3ds _{1/2}	2.907
Ar	2p	1.011	Fe	2p	2.686	Nd	3d	4.697	Sn	3ds _{1/2}	4.095
As	3d	0.570	Ga	2p _{3/2}	3.341	Ne	1s	1.340	Sr	3d	1.578
Au	4f	5.240	Gd	4d	2.207	Ni	2p	3.653	Ta	4f	2.589
B	1s	0.159	Ge	2p _{3/2}	3.100	O	1s	0.711	Tb	4d	2.201
Ba	4d	2.627	Hf	4f	2.221	Os	4f	3.747	Tc	3d	3.266
Be	1s	0.074	Hg	4f	5.797	P	2p	0.412	Te	3ds _{1/2}	4.925
Bi	4f	7.632	Ho	4d	2.189	Pb	4f	6.968	Th	4f _{7/2}	7.498
Br	3d	0.895	I	3ds _{1/2}	5.337	Pd	3d	4.642	Ti	2p	1.798
C	1s	0.296	In	3ds _{1/2}	3.777	Pm	3d	3.754	Tl	4f	6.447
Ca	2p	1.634	Ir	4f	4.217	Pr	3d	6.356	Tm	4d	2.172
Cd	3ds _{1/2}	3.444	K	2p	1.300	Pt	4f	4.674	U	4f _{5/2}	8.476
Ce	3d	7.399	Kr	3d	1.096	Rb	3d	1.316	V	2p	1.912
Cl	2p	0.770	La	3d	7.708	Re	4f	3.327	W	4f	2.959
Co	2p	3.255	Li	1s	0.025	Rh	3d	4.179	Xe	3ds _{1/2}	5.702
Cr	2p	2.201	Lu	4d	2.156	Ru	3d	3.696	Y	3d	1.867
Cs	3ds _{1/2}	6.032	Mg	2s	0.252	S	2p	0.570	Yb	4d	2.169
Cu	2p	4.798	Mn	2p	2.420	Sb	3ds _{1/2}	4.473	Zn	2p _{3/2}	3.354
Dy	4d	2.198	Mo	3d	2.867	Sc	2p	1.678	Zr	3d	2.216
Er	4d	2.184	N	1s	0.477	Se	3d	0.722			

Provided by
the maker of
the
spectrometer



$$I_i(nl) = C_i \lambda(E_{kin}) \phi(\hbar\omega) \sigma_{nl}(\hbar\omega) T(E_{kin})$$

Once the efficiency of detection of an atomic species is calibrated via the sensitivity factors one gets

Homogeneous binary compound :

$$\frac{I_A}{I_B} = \frac{S_A N_A \lambda(E_A)}{S_B N_B \lambda(E_B)}$$

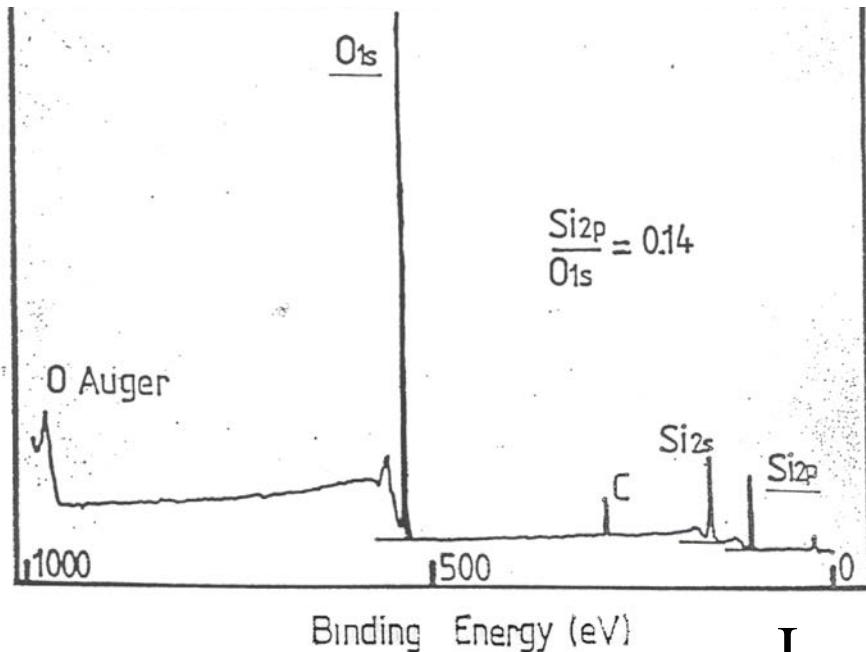
Sample with many components :

Atomic concentration C_A for each element can be determined

$$C_A = \frac{N_A}{\sum_i N_i} = \frac{I_A/[S_A \lambda(E_A)]}{\sum_i I_i/[S_i \lambda(E_i)]}$$



Example: stoichiometry of SiO₂ surface



$$\frac{I_{Si2p}}{I_{O1s}} = \frac{S_{Si2p} N_{Si} \lambda(Si2p)}{S_{O1s} N_O \lambda(O1s)} = 0,14$$

$$\frac{S_{O1s}}{S_{Si2p}} = 5,2 \quad \frac{\lambda(O1s)}{\lambda(Si2p)} = 0,76$$

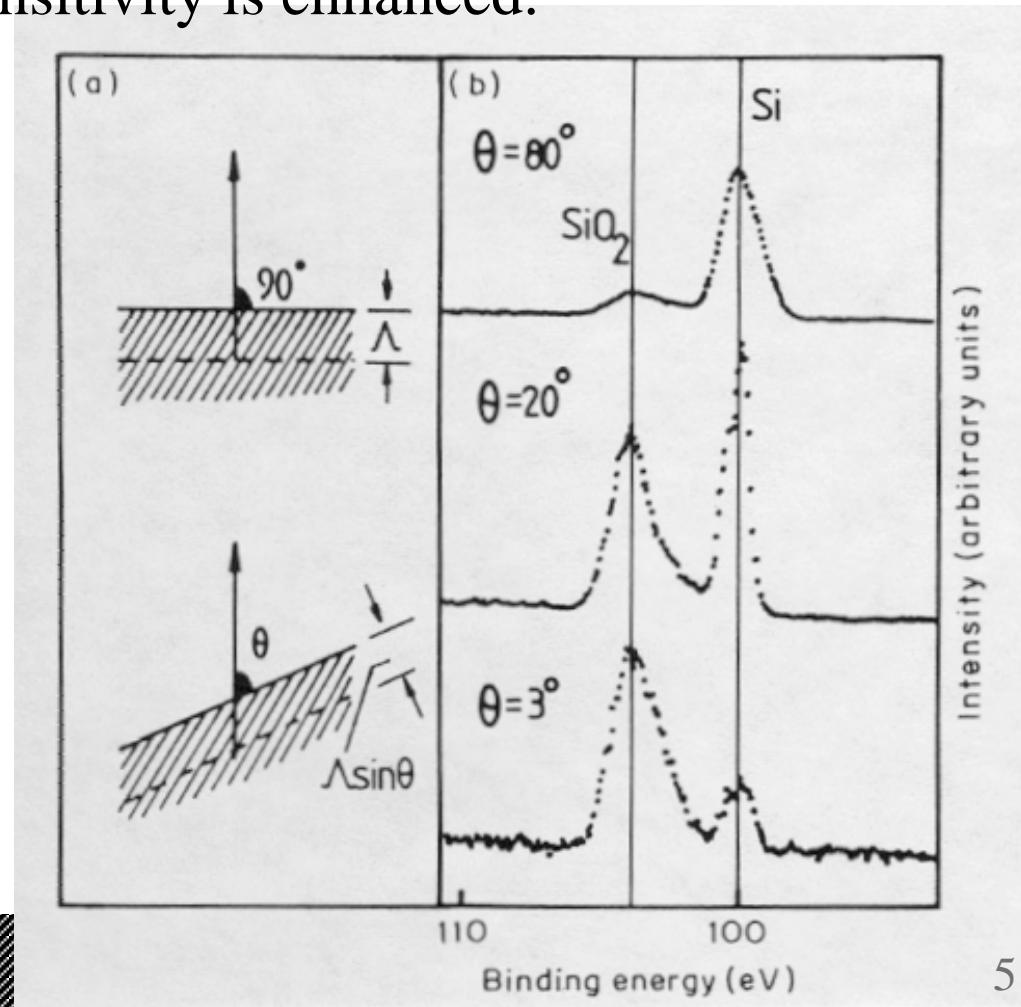
$$[Si]/[O] = 0,14 \times 5,2 \times 0,76 = 0,55$$



XPS : depth profiling via angular dependence

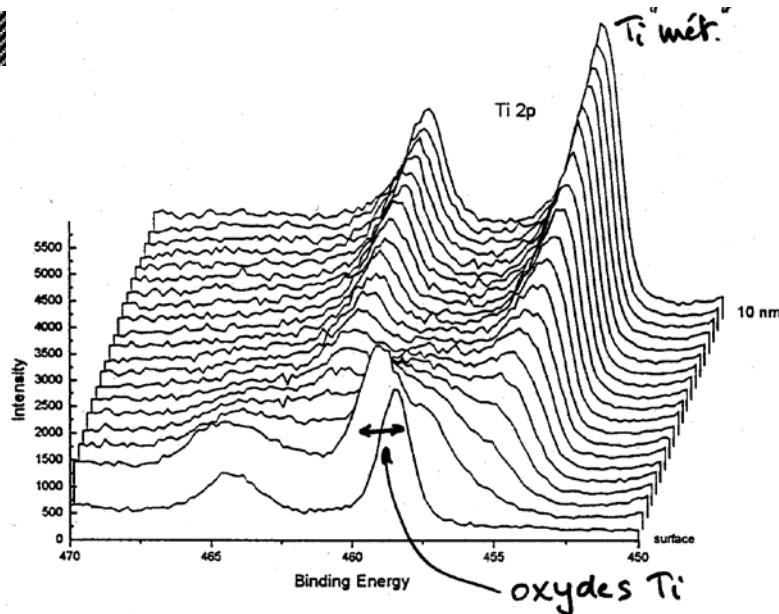
By changing experimental geometry from normal emission to grazing emission surface sensitivity is enhanced.

Example:
oxidised Si substrate



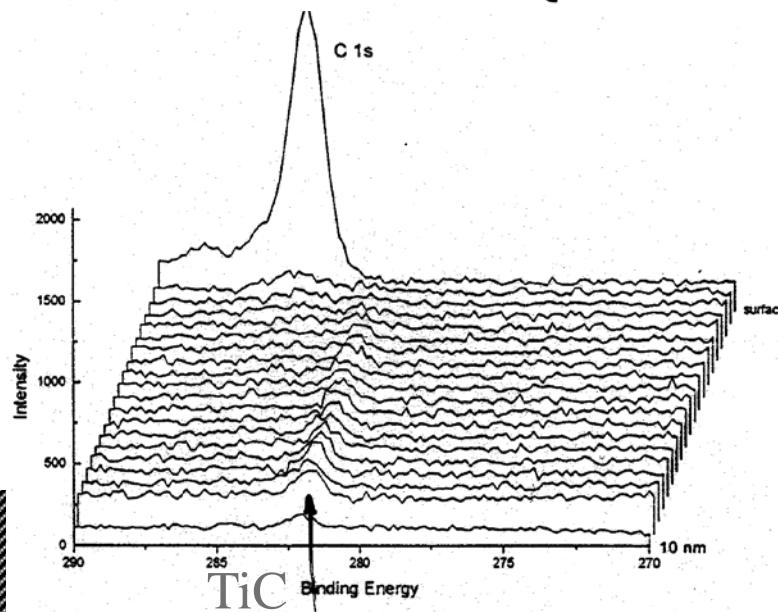


XPS : depth profiling via sputtering and measuring cycles - Destructive!



- ion sputtering - removes surface layers
- depth calibrated with reference sample

Ti 2p region

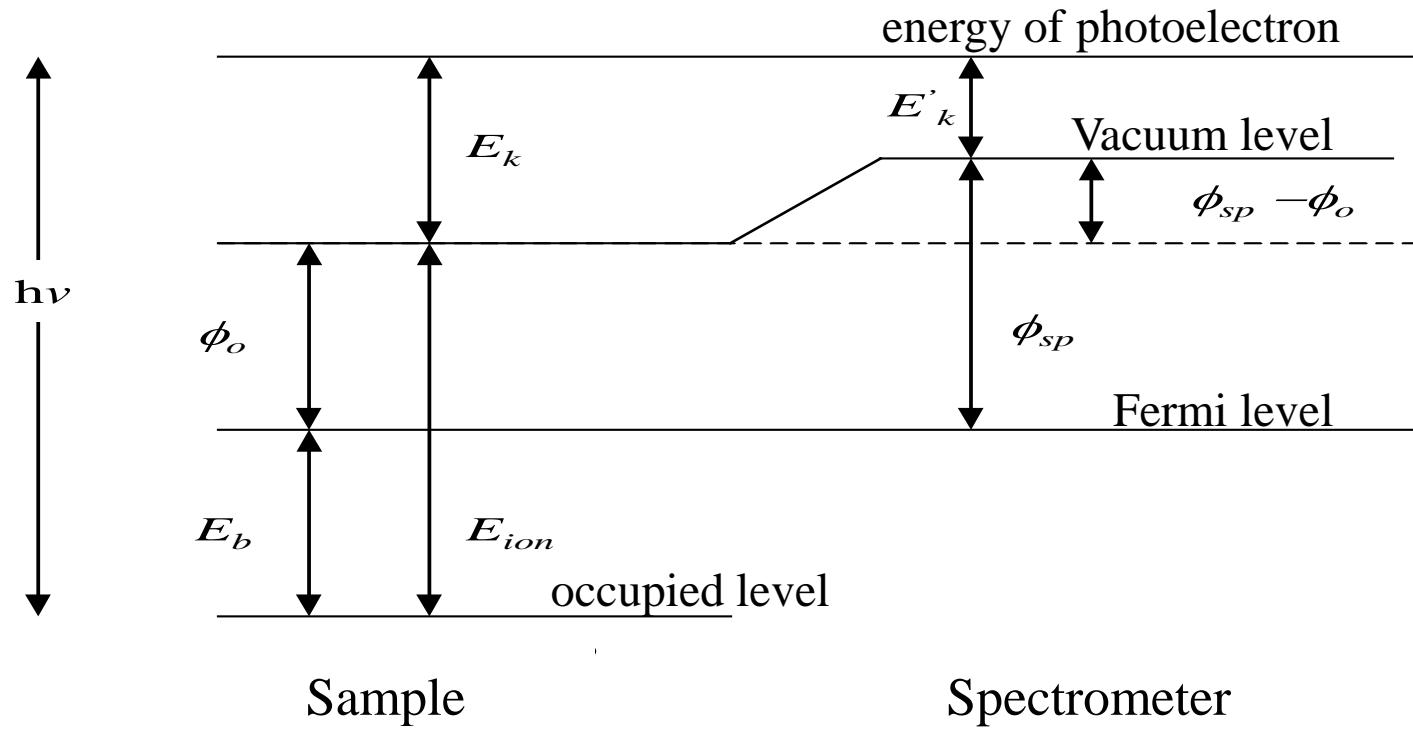


C 1s region

Example: Dental implants, surface oxidized to create porous layer which favours bone adhesion. Can determine thickness of oxide layer; can show hydrocarbon contamination at surface and carbide contamination in bulk



What is the binding energy in XPS ?



$$h\nu = E_b + E_k + \phi_0$$

$$E_b = E_f - E_i = h\nu - E' k + \phi_{sp}$$



Energy reference

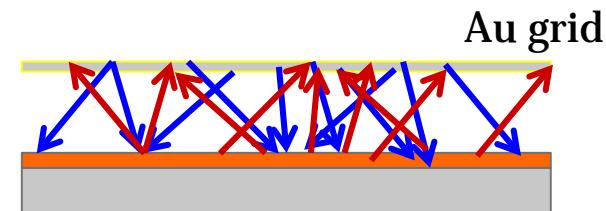
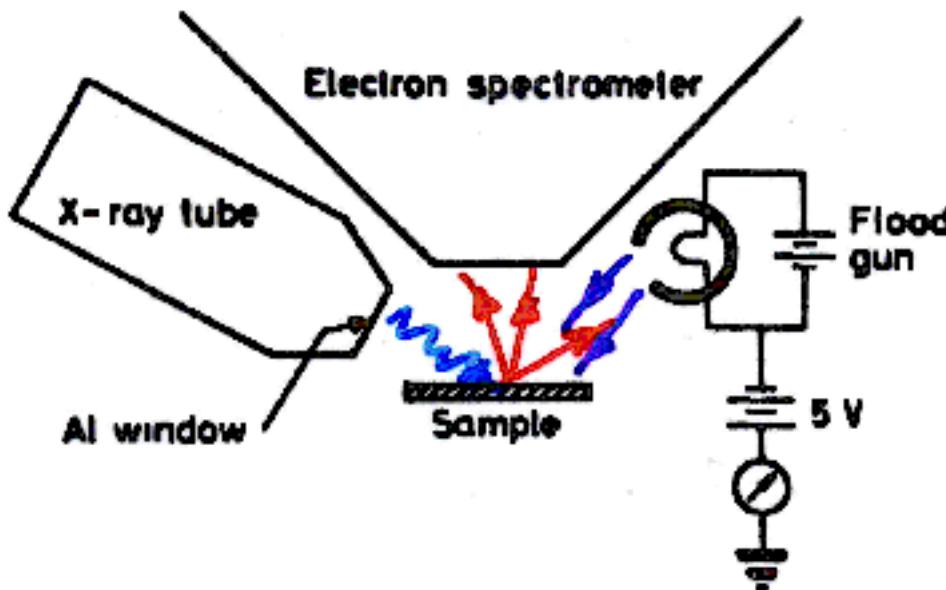
conducting samples : Fermi level

- non-conducting samples : Vacuum level

- insulating samples \Rightarrow charge effect

- $E_b = h\nu + E'_{\text{kin}} - \phi_{\text{sp}} + \Delta E$

sample has to be flooded with low energy electrons.



Photoelectrons generate secondary electrons which compensate charge



Some applications

- **quantify surface stoichiometry**
- **verify valence state of metal of nanoparticles**
- **verify core/shell structure**
- **determine growth mode of thin film**
- **verify in-situ ion transport (battery)**



High kinetic energy XPS

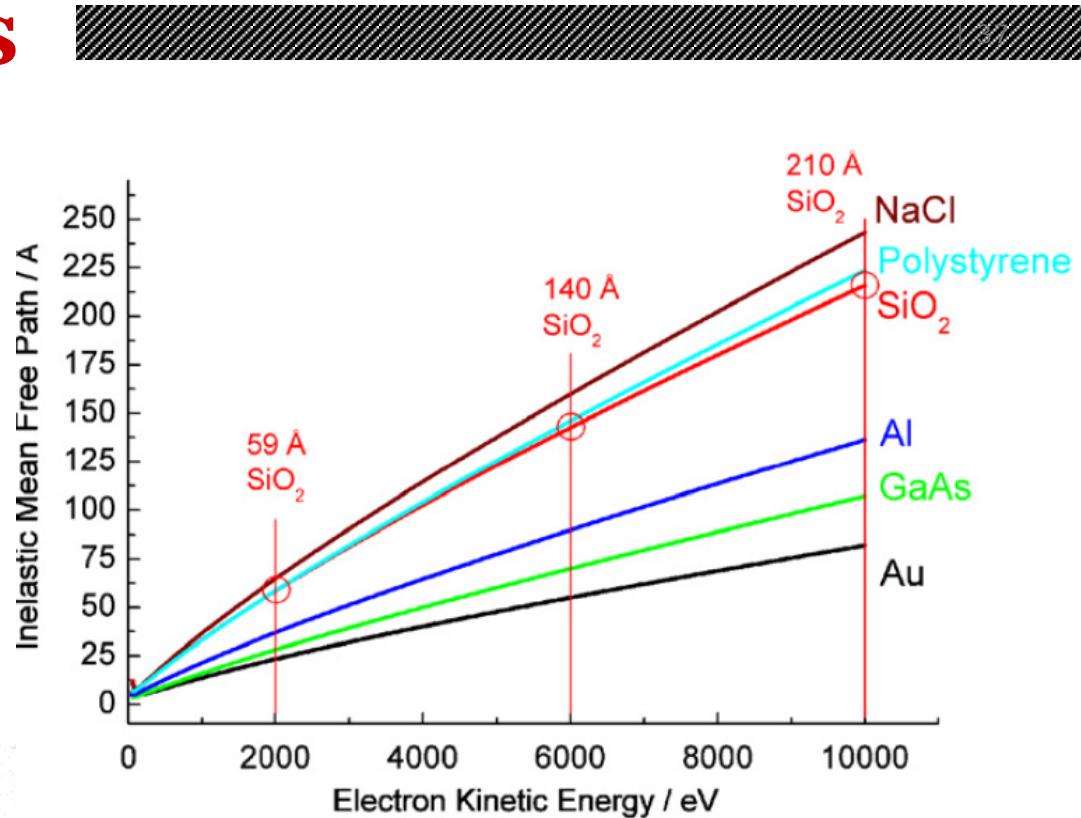
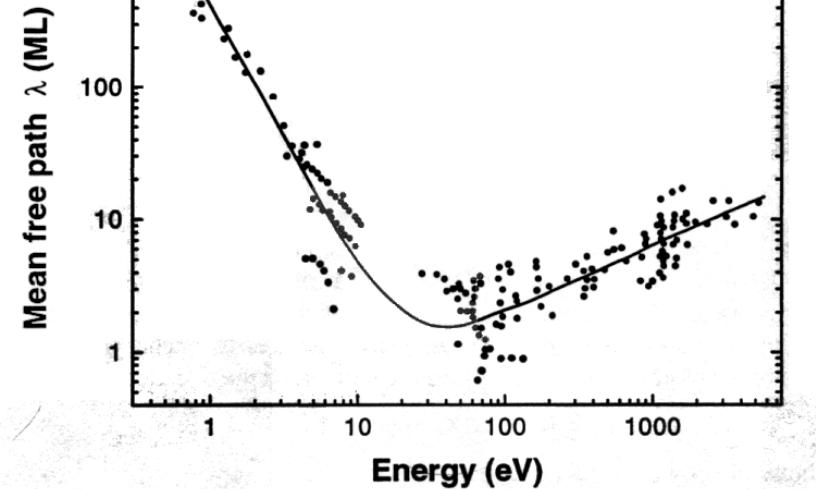
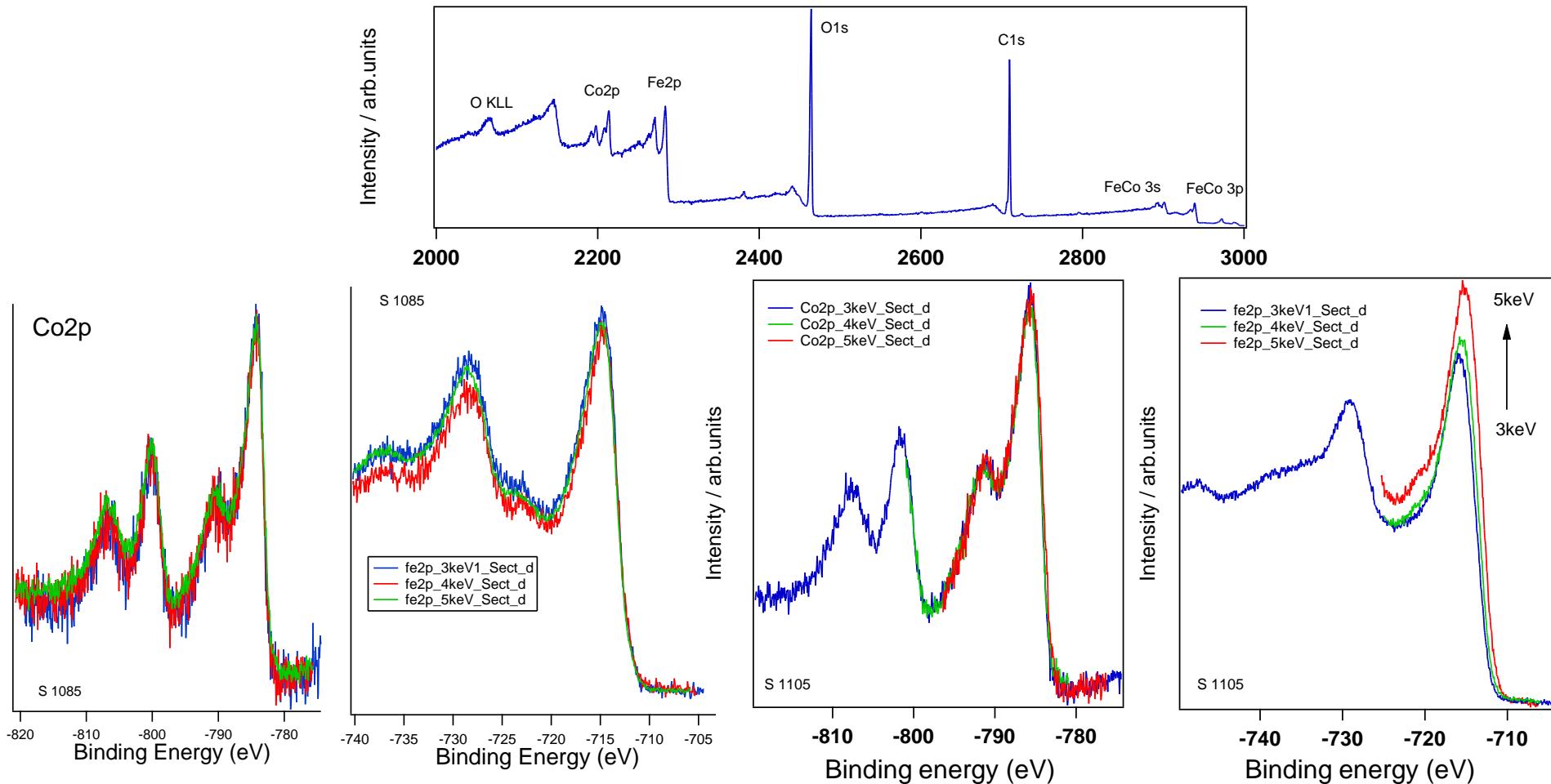


Fig. 1. Inelastic mean free path as function of electron kinetic energy for selected materials. Calculation using the NIST electron inelastic mean-free-path database, version 1.1 [3]. The HIKE facility operates between 2 and 10 keV.



FeCoO/FeO shell-core nanoparticles



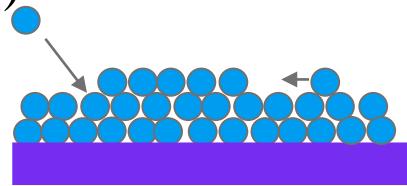
Sample A: No shell-core structure

Sample B: shows the expected shell-core structure. Co²⁺ and Fe 2+ / 3+ are present in the shell and a supposed Fe3+ phase emerge when probing deeper

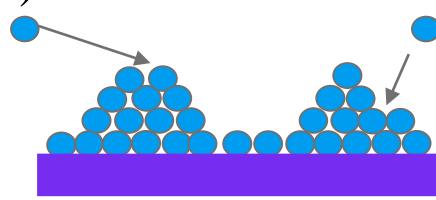


With XPS we can determine the growth mode of a film

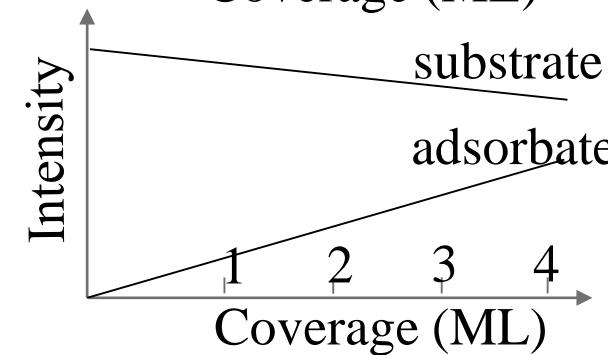
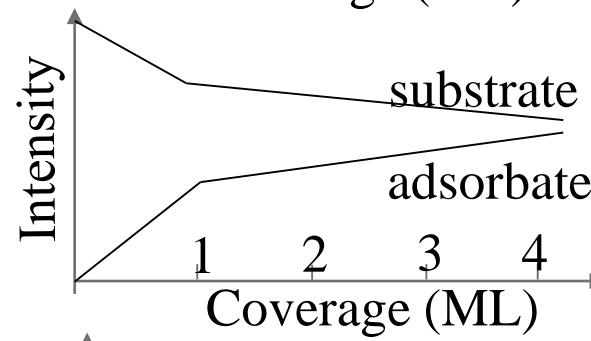
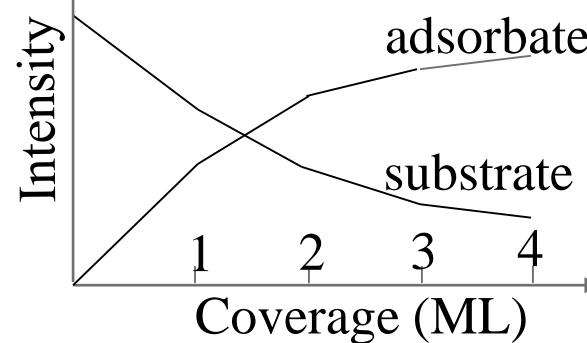
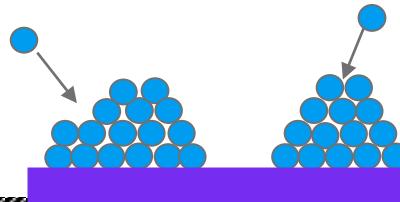
Layer by layer growth (Franck-van der Merwe)



Layer plus island growth (Stransky Krastanov)

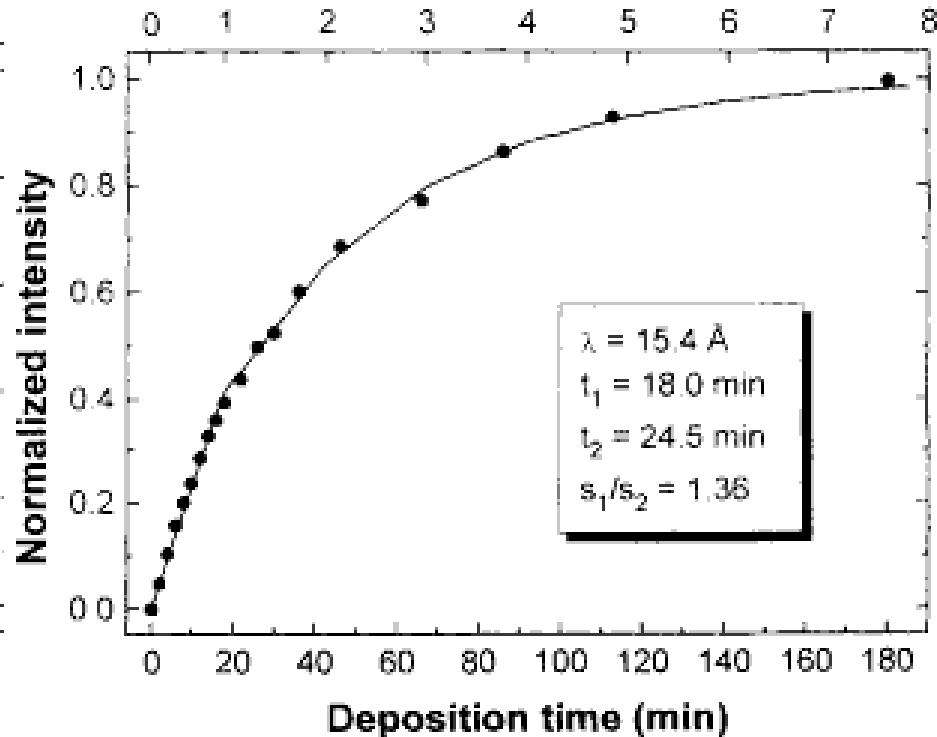
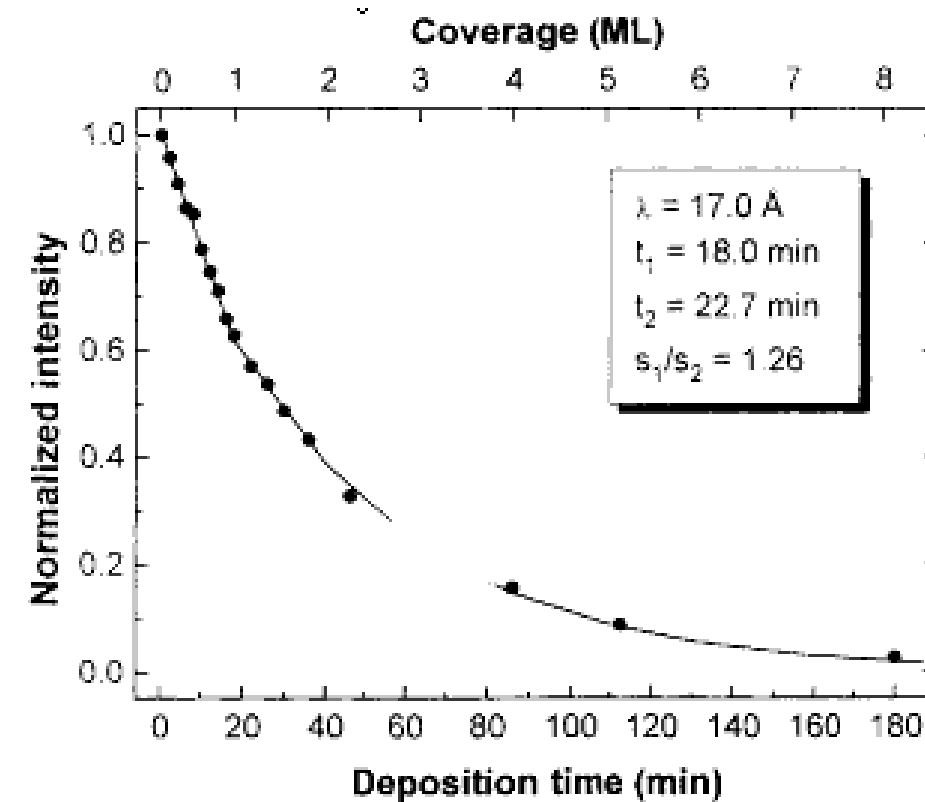


Island growth (Vollmer-Weber)





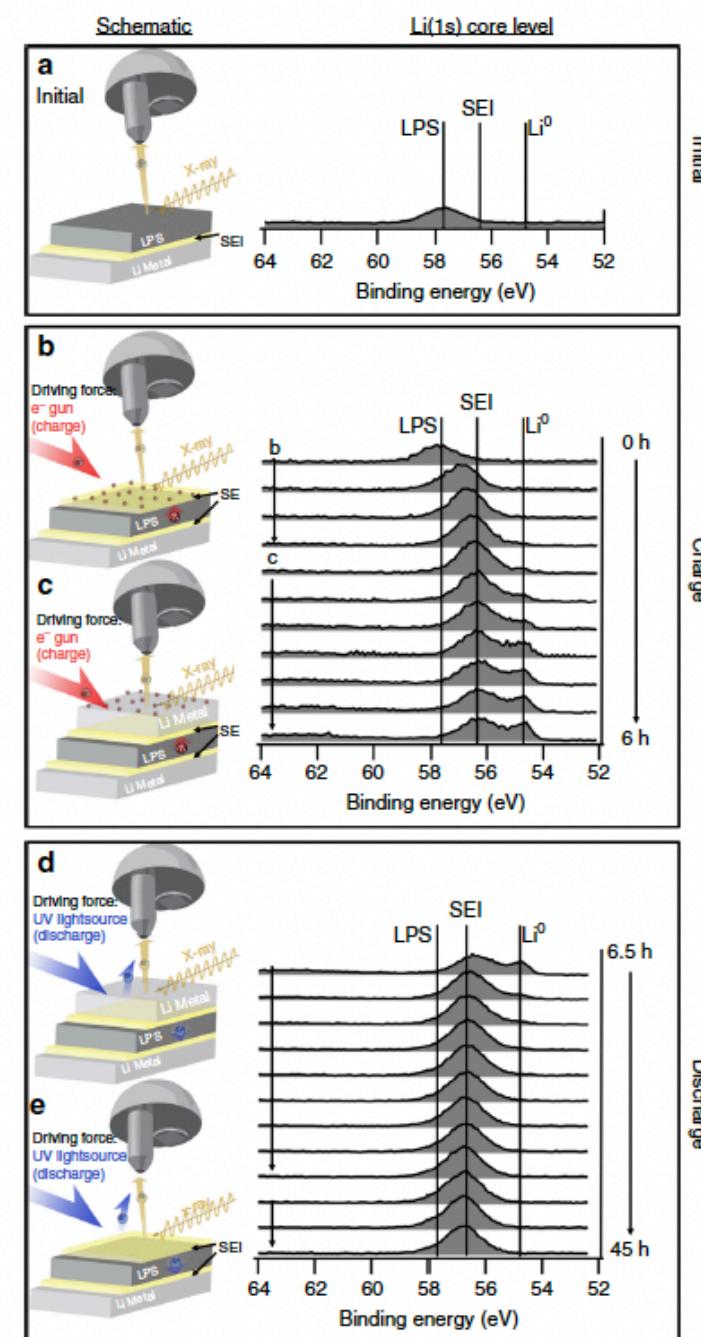
Film growth mode seen in photoemission: C₆₀(111)/GeS(001)



G. Gensterblum et al.,
PRB50 ('94) 11981



Operando XPS of solid electrolyte interphase formation and evolution in $\text{Li}_2\text{S}-\text{P}_2\text{S}_5$ solid-state electrolytes



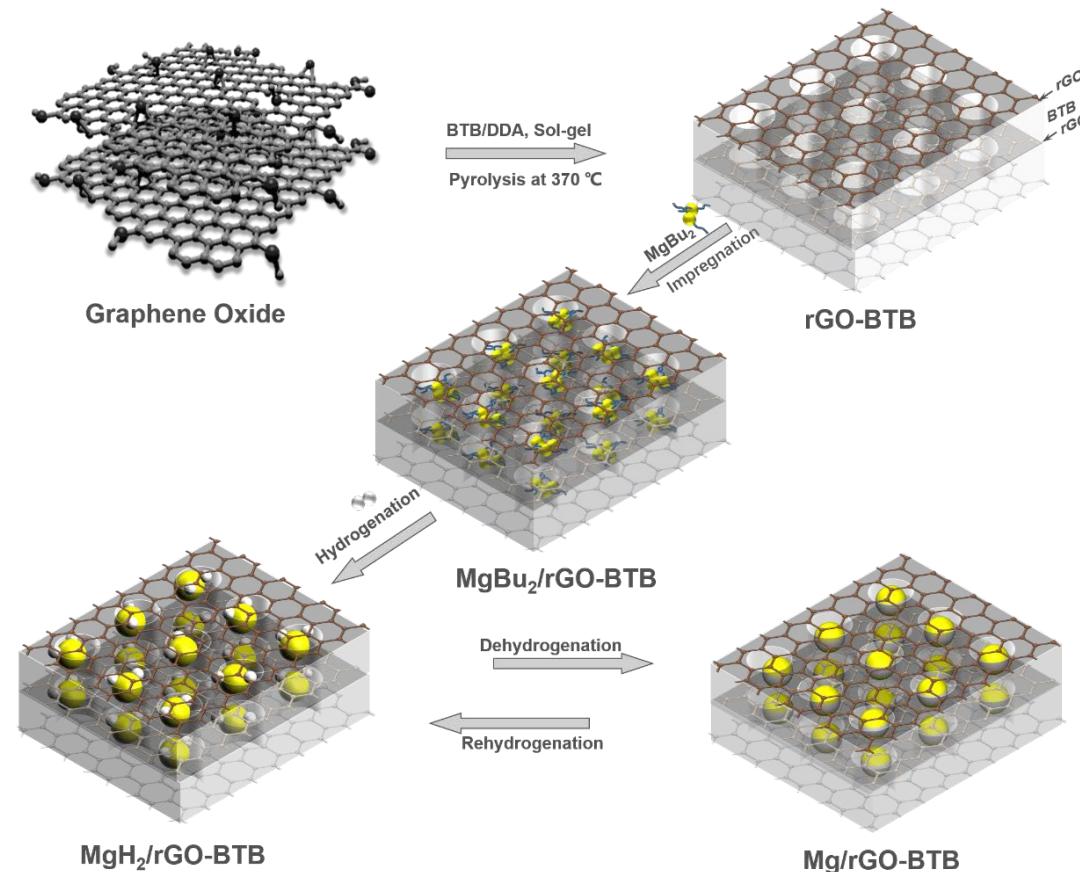
K.N. Wood *et al.* Nature Commun. (2018) 9, 2490



MgH₂ nanoparticles confined in reduced graphene oxide pillared with organosilica: a novel type of hydrogen storage material

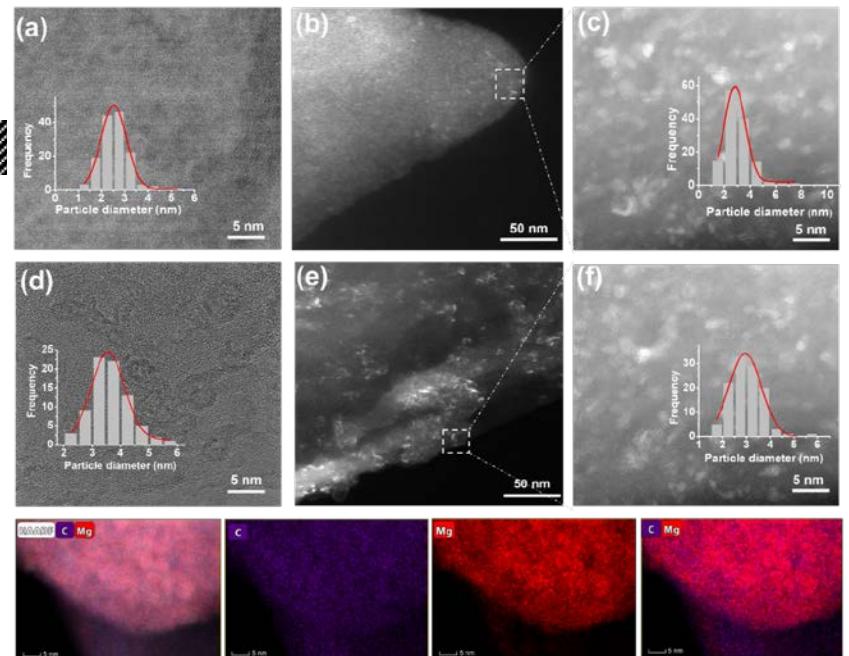
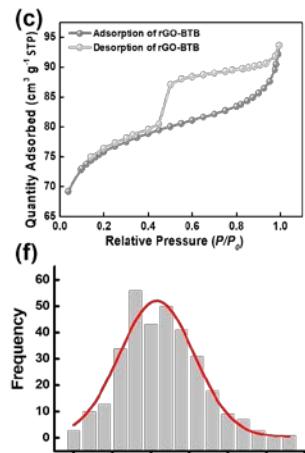
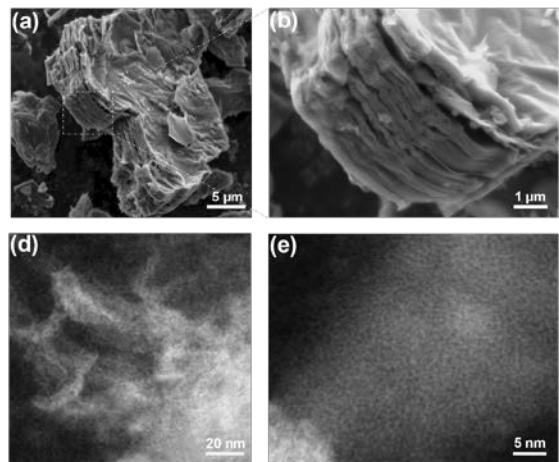
1, 4-bis(triethoxysilyl)benzene (BTB) –
pillars to distance GO planes

di-n-butylmagnesium (MgBu₂)
 $\text{MgBu}_2 + \text{H}_2 \rightarrow \text{MgH}_2 + 2\text{C}_4\text{H}_{10}\uparrow$

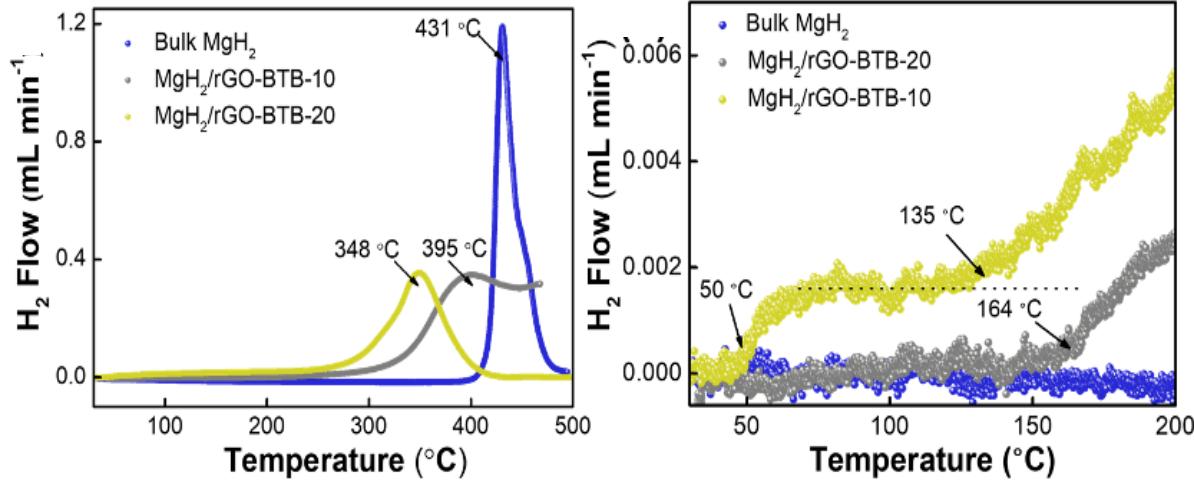




rGO-BTB-10

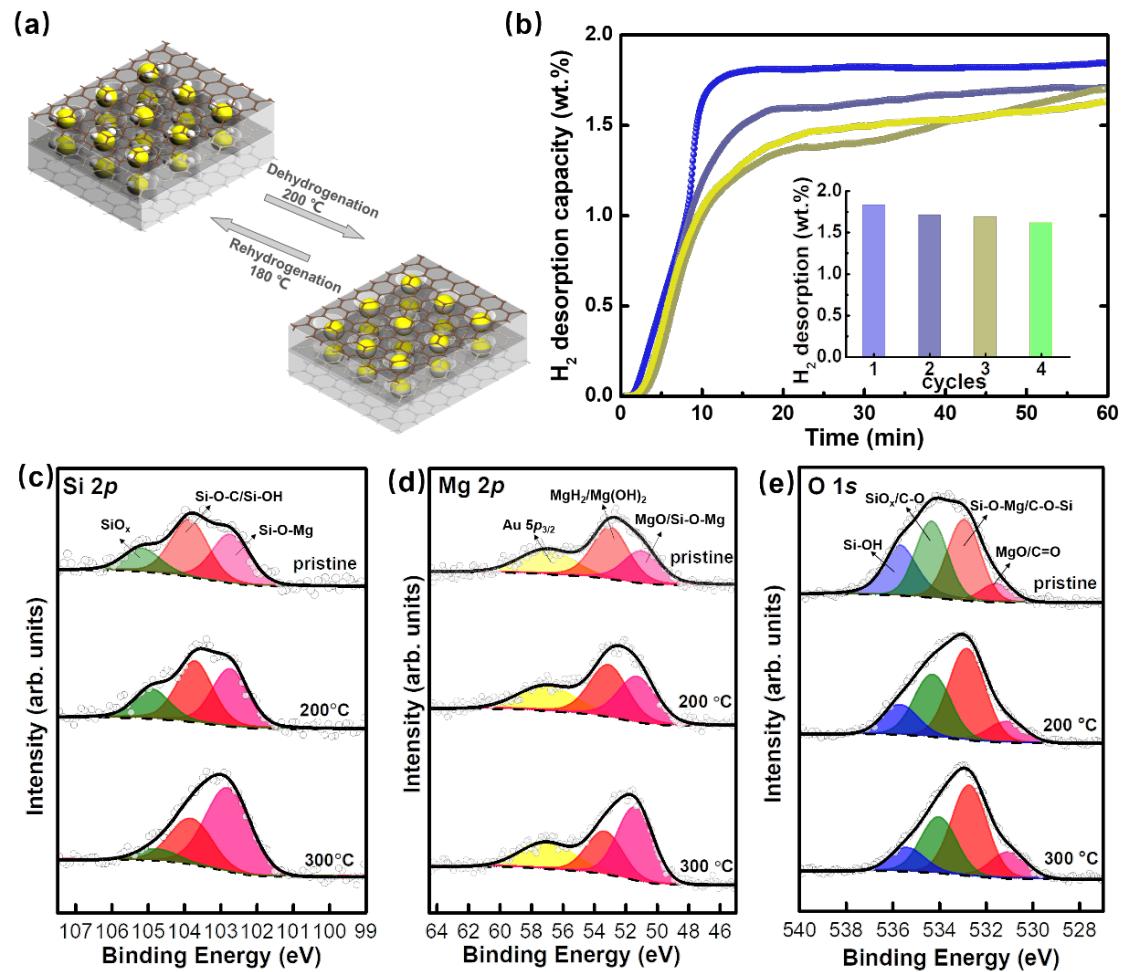


Hydrogen desorption starts at 50 °C ! efficient reversible 1.62 wt.% hydrogen storage can be realized at 200 °C





Above 200 °C Mg reacts with silanol groups





XPS summary

- all kinds of samples: solid, liquid, gases in vacuum (10^{-8} torr)
- both insulating and conducting samples
- can detect most elements at the 0.1% level (not H, He)
- non-destructive (X-ray beam damage possible)
- surface sensitive
- quantitative analysis possible
- determination of oxidation state possible
- depth profiling : through angular dependence (non-destructive) or sputtering-measuring cycles (destructive)



Thank you for your attention!

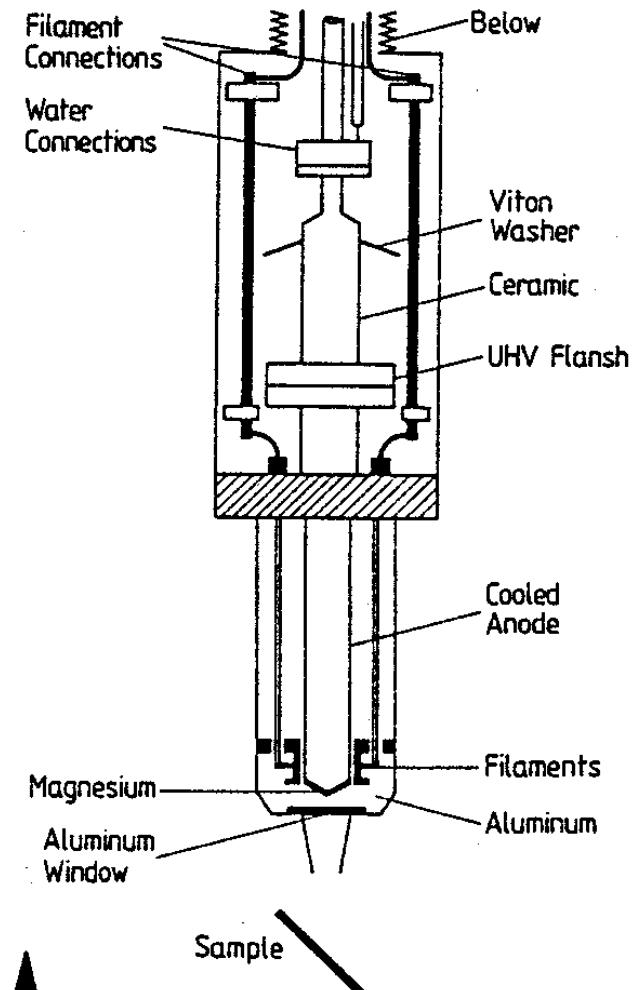


Experimental details

X-ray Sources :

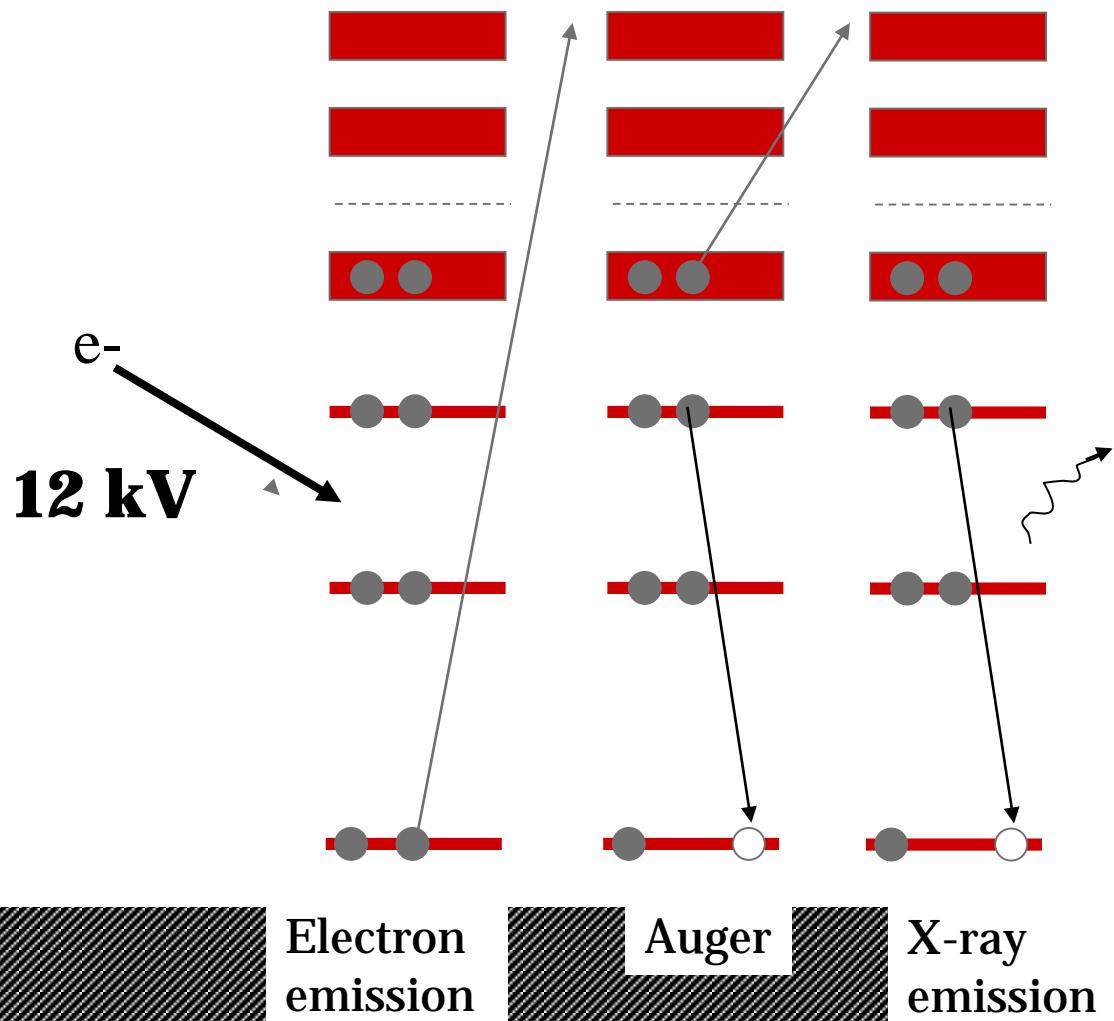
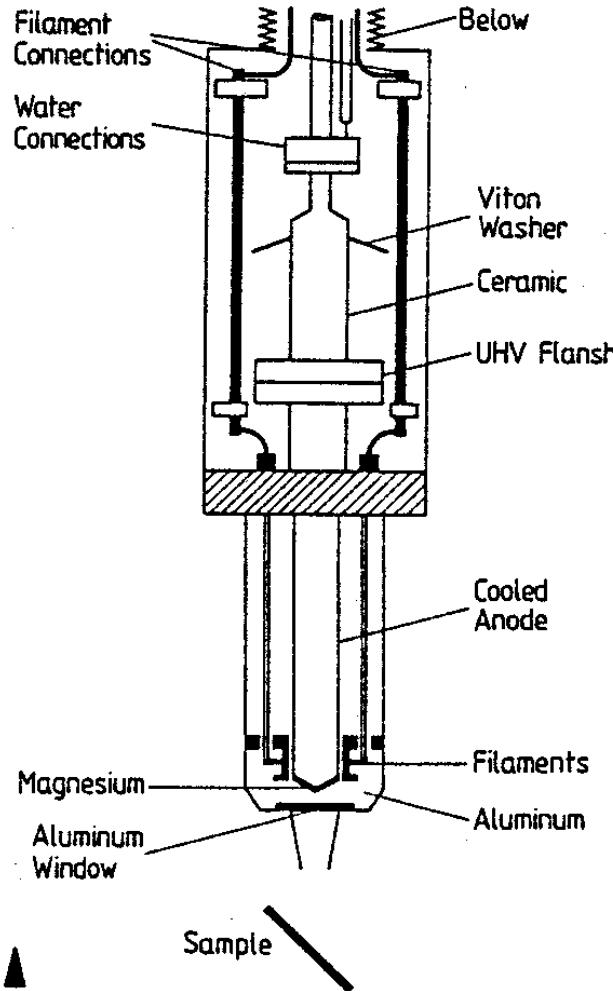
- Monochromatic laboratory sources
 $Mg\ K_{\alpha}$ 1253,6 eV or $Al\ K_{\alpha}$ 1486,6 eV
- synchrotron radiation \Rightarrow photon energy can be chosen between 200 and 1500 eV

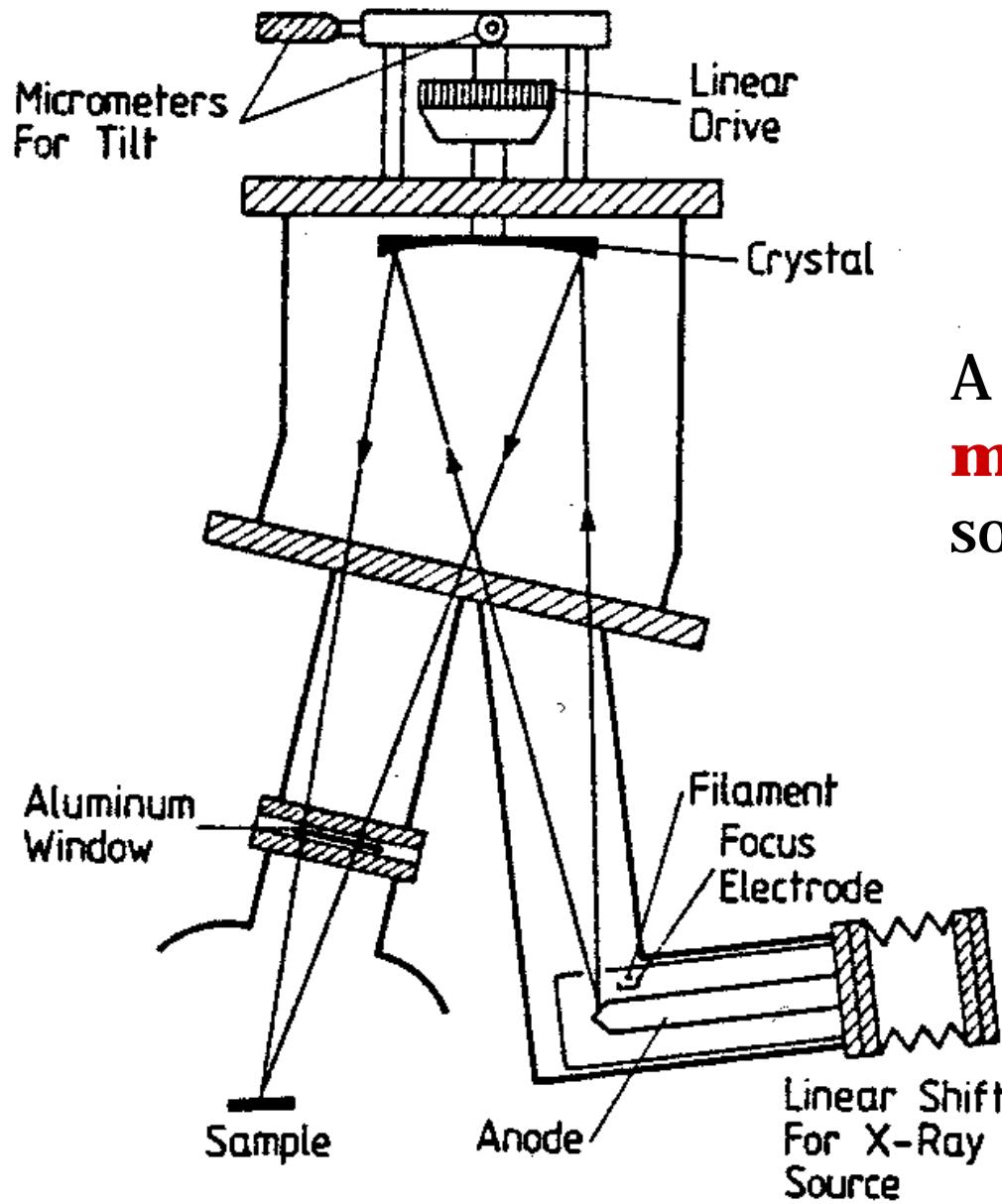
A standard **X-Ray source** –
has to be coupled to
monochromator



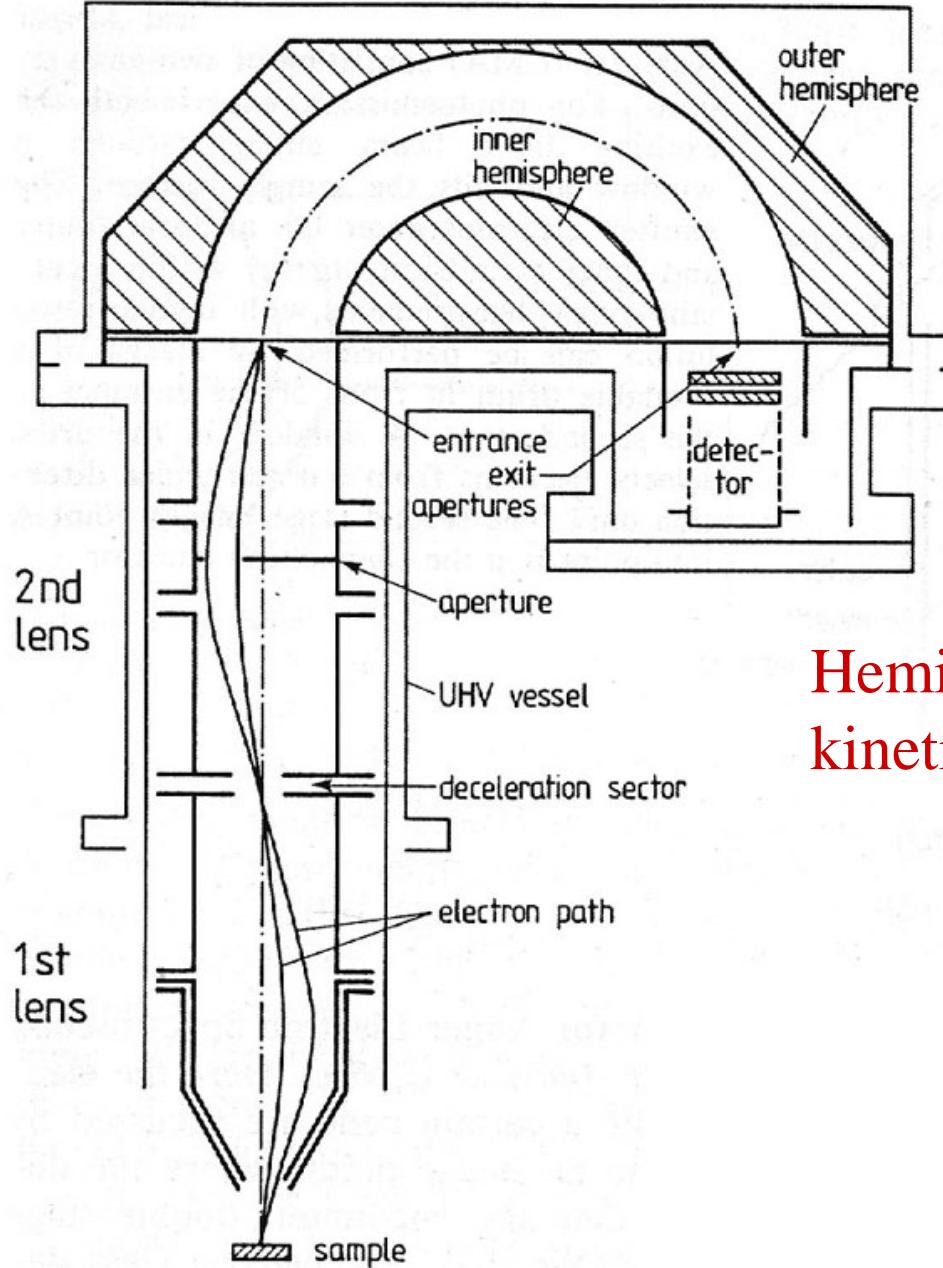


X-Ray source





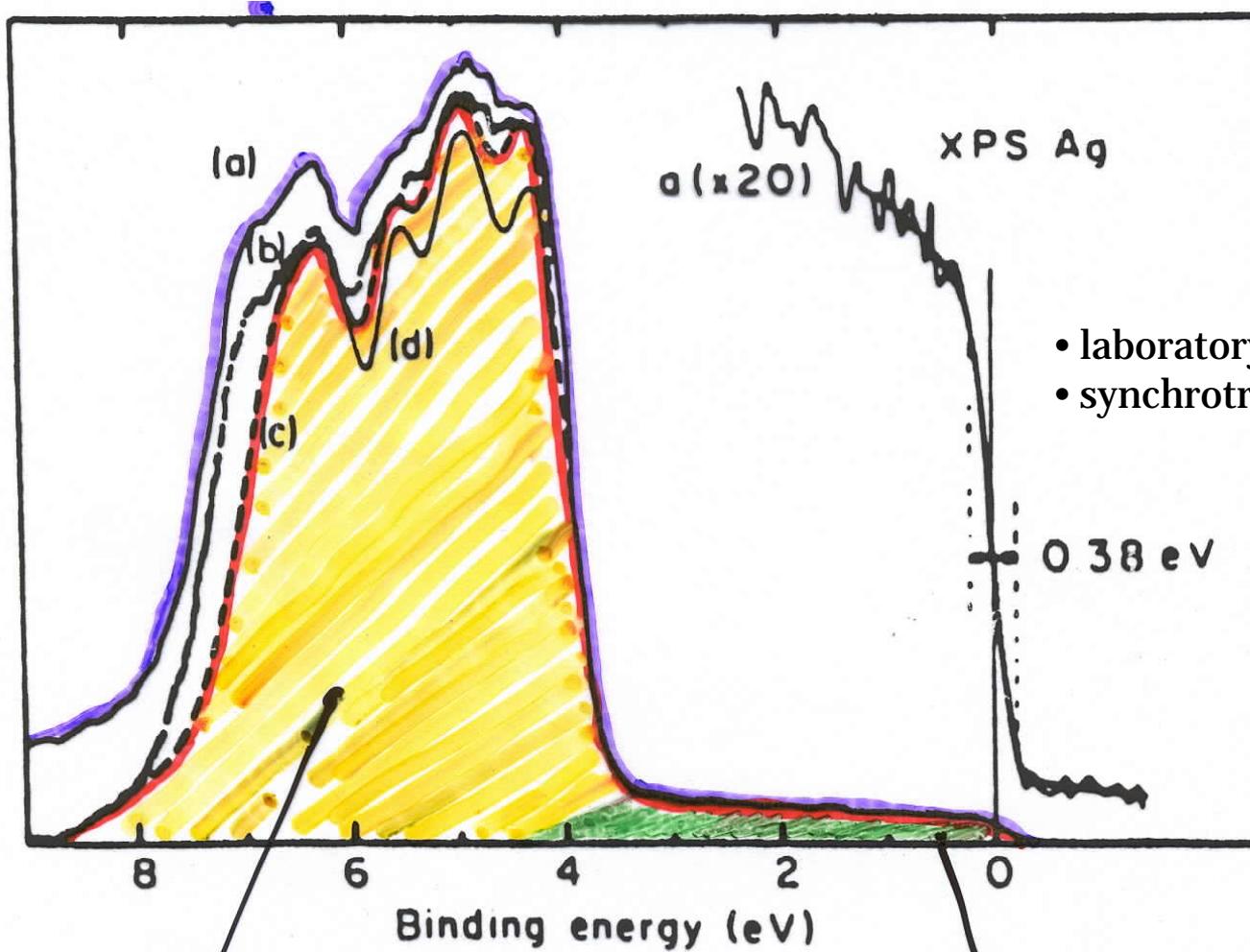
A standard
monochromator for X-Ray
source



Hemispherical analyzer of electron kinetic energy



The **instrumental resolution** can be determined by measuring the Fermi edge of a metallic sample



Ag 4d-related manyfold

Ag 5(sp)-related manyfold